







TPS6521845 SLDS267A - NOVEMBER 2020 - REVISED AUGUST 2021

TPS6521845 Power Management IC (PMIC) for NXP i.MX 6Solo and 6DualLite

1 Features

- Three Adjustable Step-Down Converters With Integrated Switching FETs (DCDC1, DCDC2, and DCDC3):
 - DCDC1: 1.425-V Default, up to 1.8 A
 - DCDC2: 1.425-V Default, up to 1.8 A
 - DCDC3: 1.5-V Default, up to 1.8 A
 - VIN Range From 2.7 V to 5.5 V
 - Adjustable Output Voltage Range 0.85 V to 1.675 V (DCDC1 and DCDC2)
 - Adjustable Output Voltage Range 0.9 V to 3.4 V (DCDC3)
 - Power Save Mode at Light Load Current
 - 100% Duty Cycle for Lowest Dropout
 - Active Output-Discharge When Disabled
- One Adjustable Buck-Boost Converter With Integrated Switching FETs (DCDC4):
 - DCDC4: 3.3-V Default, up to 1.6 A
 - VIN Range from 2.7 V to 5.5 V
 - Adjustable Output Voltage Range from 1.175 V to 3.4 V
 - Active Output-Discharge When Disabled
- Two Low-Quiescent Current, High Efficiency Step-Down Converters for Battery Backup Domain (DCDC5, DCDC6)
 - DCDC5: 1-V Output
 - DCDC6: 1.8-V Output
 - VIN Range from 2.2 V to 5.5 V
 - Supplied From System Power or Coin-Cell Backup Battery
- Adjustable General-Purpose LDO (LDO1)
 - LDO1: 1.8-V Default up to 400 mA
 - VIN Range from 1.8 V to 5.5 V
 - Adjustable Output Voltage Range from 0.9 V to 3.4 V
 - Active Output-Discharge When Disabled
- Low-Voltage Load Switch (LS1) With 350-mA Current Limit
 - VIN Range From 1.2 V to 3.6 V
 - 110-mΩ (Max) Switch Impedance at 1.35 V
- 5-V Load Switch (LS2) With 100-mA or 500-mA Selectable Current Limit
 - VIN Range From 4 V to 5.5 V
 - 500-mΩ (Max) Switch Impedance at 5 V
- High-Voltage Load Switch (LS3) With 100-mA or 500-mA Selectable Current Limit
 - VIN Range From 1.8 V to 10 V
 - 500-mΩ (Max) Switch Impedance
- Supervisor With Built-in Supervisor Function Monitors

- DCDC1, DCDC2 ±4% Tolerance
- DCDC3, DCDC4 ±5% Tolerance
- LDO1 ±5% Tolerance
- Protection, Diagnostics, and Control:
 - Undervoltage Lockout (UVLO)
 - Always-on Push-Button Monitor
 - Overtemperature Warning and Shutdown
 - Separate Power-Good Output for Backup and Main Supplies
 - I²C Interface (Address 0x24) (See *Timing* Requirements for I²C Operation at 400 kHz)

2 Applications

- Human-Machine Interface (HMI)
- **Industrial Automation**
- Electronic Point of Sale (ePOS)
- **Test and Measurement**
- **Personal Navigation**

3 Description

The TPS6521845 is a single chip power management IC, specifically designed to support both portable (Li-lon battery) and non-portable (5-V adapter) applications. The device is characterized across a -40°C to +105°C temperature range, making it suitable for a wide range of industrial applications.

Device Information⁽¹⁾

		PACKAGE	BODY SIZE (NOM)
	TPS6521845	VQFN (48)	6.00 mm × 6.00 mm

For all available packages, see the orderable addendum at the end of the data sheet



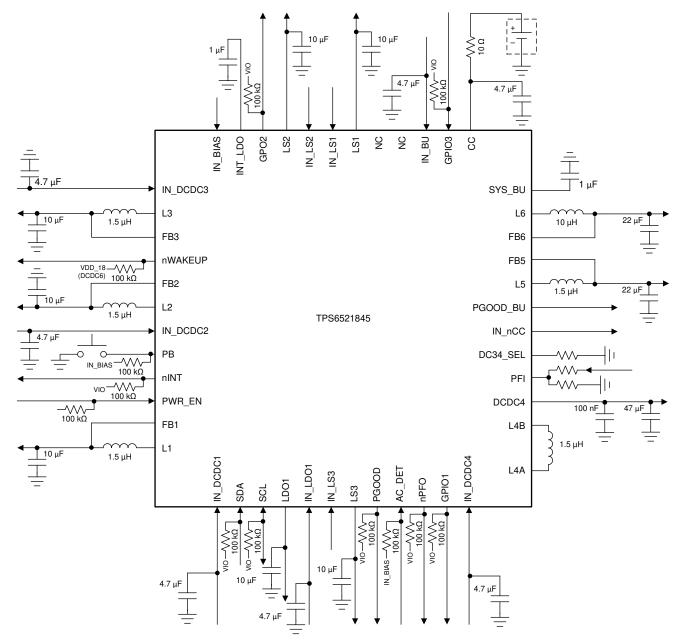


Figure 3-1. Simplified Schematic



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	changes from Revision * (November 2020) to Revision A (August 2021)	Page
•	Changed DCDC1 default voltage from 1.1-V to 1.425-V	
•	Changed DCDC2 default voltage from 1.1-V to 1.425-V	
•	Changed DCDC3 default voltage from 1.2-V to 1.5-V	



5 Pin Configuration and Functions

Figure 5-1 shows the 48-pin RSL Plastic Quad Flatpack No-Lead.

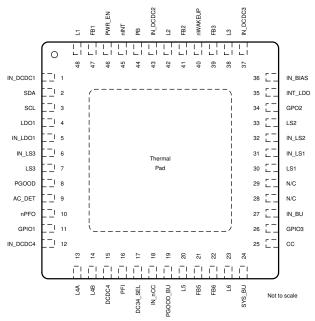


Figure 5-1. 48-Pin RSL VQFN With Exposed Thermal Pad (Top View, 6 mm × 6 mm × 1 mm With 0.4-mm Pitch)

Table 5-1. Pin Functions

	PIN	TYPE	DESCRIPTION				
NO.	NAME	ITPE	DESCRIPTION				
1	IN_DCDC1	Р	Input supply pin for DCDC1.				
2	SDA	I/O	e for the I ² C interface. Connect to pullup resistor.				
3	SCL	I	Clock input for the I ² C interface. Connect to pullup resistor.				
4	LDO1	0	Output voltage pin for LDO1. Connect to capacitor.				
5	IN_LDO1	Р	Input supply pin for LDO1.				
6	IN_LS3	Р	Input supply pin for load switch 3.				
7	LS3	0	Output voltage pin for load switch 3. Connect to capacitor.				
8	PGOOD	0	Power-good output (configured as open drain). Pulled low when either DCDC1-4 or LDO1 are out of regulation. Load switches and DCDC5-6 do not affect PGOOD pin.				
9	AC_DET	I	AC monitor input and enable for DCDC1-4, LDO1 and load switches. See Section 7.4.1 for details. Tie pin to IN_BIAS if not used.				
10	nPFO	0	Power-fail comparator output, deglitched (open drain). Pin is pulled low when PFI input is below power-fail threshold.				
11	GPIO1	I/O	Pin configured as DDR reset-input (driving GPO2) or as general-purpose, open-drain output. See Section 7.3.1.14 for more information.				
12	IN_DCDC4	Р	Input supply pin for DCDC4.				
13	L4A	Р	Switch pin for DCDC4. Connect to inductor.				
14	L4B	Р	Switch pin for DCDC4. Connect to inductor.				
15	DCDC4	Р	Output voltage pin for DCDC4. Connect to capacitor.				
16	PFI	I	Power-fail comparator input. Connect to resistor divider.				
17	DC34_SEL	I	Power-up default selection pin for DCDC3 or DCDC4. Power-up default is programmed by a resistor connected to ground. See Section 7.3.1.13 for resistor options.				

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Table 5-1. Pin Functions (continued)

	PIN					
NO.	NAME	TYPE	DESCRIPTION			
18	IN_nCC	0	Output pin indicates if DCDC5 and DCDC6 are powered from main supply (IN_BU) or coin-cell battery (CC). Pin is push-pull output. Pulled low when PMIC is powered from coin cell battery. Pulled high when PMIC is powered from main supply (IN_BU).			
19	PGOOD_BU	0	Power-good, push-pull output for DCDC5 and DCDC6. Pulled low when either DCDC5 or DCDC6 is out of regulation. Pulled high (to DCDC6 output voltage) when both rails are in regulation.			
20	L5	Р	Switch pin for DCDC5. Connect to inductor.			
21	FB5	I	Feedback voltage pin for DCDC5. Connect to output capacitor.			
22	FB6	I	Feedback voltage pin for DCDC6. Connect to output capacitor.			
23	L6	Р	Switch pin for DCDC6. Connect to inductor.			
24	SYS_BU	Р	System voltage pin for battery-backup supply power path. Connect to 1-µF capacitor. Connecting any external load to this pin is not recommended.			
25	СС	Р	Coin cell battery input. Serves as the supply to DCDC5 and DCDC6 if no voltage is applied to IN_BU. Tie this pin to ground if it is not in use.			
26	GPIO3	I/O Pin can be configured as warm reset (negative edge) for DCDC1 and DCDC2 or as a general-purpose, open-drain output. See Section 7.3.1.14 for more details.				
27	IN_BU	Р	Default input supply pin for battery backup supplies (DCDC5 and DCDC6).			
28	N/C		No connect Leave his fleeting			
29	N/C	_	No connect. Leave pin floating.			
30	LS1	0	Output voltage pin for load switch 1. Connect to capacitor.			
31	IN_LS1	Р	Input supply pin for load switch 1.			
32	IN_LS2	Р	Input supply pin for load switch 2.			
33	LS2	0	Output voltage pin for load switch 2. Connect to capacitor.			
34	GPO2	0	Pin configured as DDR reset signal (controlled by GPIO1) or as general-purpose output. Buffer can be configured as push-pull or open-drain.			
35	INT_LDO	Р	Internal bias voltage. Connecting any external load to this pin is not recommended.			
36	IN_BIAS	Р	Input supply pin for reference system.			
37	IN_DCDC3	Р	Input supply pin for DCDC3.			
38	L3	Р	Switch pin for DCDC3. Connect to inductor.			
39	FB3	I	Feedback voltage pin for DCDC3. Connect to output capacitor.			
40	nWAKEUP	0	Signal to SOC to indicate a power on event (active low, open-drain output).			
41	FB2	I	Feedback voltage pin for DCDC2. Connect to output capacitor.			
42	L2	Р	Switch pin for DCDC2. Connect to inductor.			
43	IN_DCDC2	Р	Input supply pin for DCDC2.			
44	РВ	I	Push-button monitor input. Typically connected to a momentary switch to ground (active low). See Section 7.4.1 for details.			
45	nINT	0	Interrupt output (active low, open drain). Pin is pulled low if an interrupt bit is set. The pin returns to Hi-Z state after the bit causing the interrupt has been read. Interrupts can be masked.			
46	PWR_EN	-	Power enable input for DCDC1-4, LDO1 and load switches. See Section 7.4.1 for details.			
47	FB1		Feedback voltage pin for DCDC1. Connect to output capacitor.			
48	L1	Р	Switch pin for DCDC1. Connect to inductor.			
_	Thermal Pad	Р	Power ground and thermal relief. Connect to ground plane.			



6 Specifications

6.1 Absolute Maximum Ratings

Operating under free-air temperature range (unless otherwise noted).(1)

			MIN	MAX	UNIT	
		IN_BIAS, IN_LDO1, IN_LS2, IN_DCDC1, IN_DCDC2, IN_DCDC3, IN_DCDC4	-0.3	7		
	Supply voltage	IN_LS1, CC	-0.3	3.6	V	
		IN_LS3	-0.3	11.2		
		IN_BU	-0.3	5.8		
	Input voltage	DC34_SEL	-0.3	3.6	V	
	input voltage	All pins unless specified separately	-0.3	7] v	
	Output voltage	DC34_SEL	-0.3	3.6 V		
	Output voltage	All pins unless specified separately	-0.3	7]	
	Source or sink	GPO2		6	- mA	
	0000	PGOOD_BU, IN_nCC		1	1 IIIA	
	Sink current	PGOOD, nWAKEUP, nINT, nPFO, SDA, GPIO1, GPIO3		6	mA	
T _A	Operating ambient temperature Junction temperature		-40	105	°C	
TJ			-40	125	°C	
T _{stg}	Storage temperatu	re	-0.3 7 -0.3 3.6 -0.3 11.2 -0.3 5.8 -0.3 3.6 -0.3 7 -0.3 3.6 -0.3 7 -0.3 6 1 6 1 6 -40 105	°C		

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Licotrobtatio	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	\/
	discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

Product Folder Links: TPS6521845



6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted).

		MIN	NOM MAX	UNIT
Supply voltage, IN_BIAS		2.7	5.5	V
Input voltage for DCDC1, DCDC2	, DCDC3, and DCDC4	2.7	5.5	V
Supply voltage, IN_BU		2.2	5.5	V
Supply voltage, CC		2.2	3.3	V
Input voltage for LDO1		1.8	5.5	V
Input voltage for LS1		1.2	3.6	V
put voltage for LS2		3	5.5	V
Input voltage for LS3		1.8	10	V
Output voltage for DCDC1		0.85	1.675	V
Output voltage for DCDC2		0.85	1.675	V
Output voltage for DCDC3		0.9	3.4	V
Output voltage for DCDC4		1.175	3.4	V
Output voltage for DCDC5			1	V
Output voltage for DCDC6			1.8	V
Output voltage for LDO1		0.9	3.4	V
Output current for DCDC1, DCDC	2, and DCDC3	0	1.8	Α
	VIN_DCDC4 = 2.8 V		1	
Output current for DCDC4	VIN_DCDC4 = 3.6 V		1.3	Α
	VIN_DCDC4 = 5 V		1.6	
Output current for DCDC5 and DC	CDC6	0	25	mA
Output current for LDO1		0	400	mA
Output current for LS1		0	300	mA
Output current for LS2		0	920	mA
Output current for LS3	VIN_LS3 > 2.3 V	0	900	mA
Output cullent for £33	VIN_LS3 ≤ 2.3 V	0	475	шл

6.4 Thermal Information

		TPS6521845	
	THERMAL METRIC ⁽¹⁾	RSL (VQFN)	UNIT
		48 PINS	
R ₀ JC(top)	Junction-to-case (top)	17.2	°C/W
$R_{\theta JB}$	Junction-to-board	5.8	°C/W
$R_{\theta JA}$	Thermal resistance, junction-to-ambient. JEDEC 4-layer, high-K board.	30.6	°C/W
Ψ_{JT}	Junction-to-package top	0.2	°C/W
Ψ_{JB}	Junction-to-board	5.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom)	1.5	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



6.5 Electrical Characteristics

Over operating free-air temperature range (unless otherwise noted).

	PARAMETER	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT
INPUT VOL	TAGE AND CURRENTS						
\ /	land the same have been as a second	Normal operation		2.7		5.5	V
VIN_BIAS	Input supply voltage range	EEPROM programming		4.5		5.5	V
			UVLO[1:0] = 00b	2.7	2.75	2.8	V
\	l lo demonite na la alcació	Supply falling; measured in	UVLO[1:0] = 01b	2.85	2.95	3.05	V
V _{UVLO}	Undervoltage lockout	respect to V _{IN_BIAS}	UVLO[1:0] = 10b	3.15	3.25	5.5 5.5 2.75 2.8 2.95 3.05 3.25 3.35 3.35 3.45 200 400 0 5 5 5 220 5.5 1 20%	V
			UVLO[1:0] = 11b	3.25	3.35	3.45	V
		Supply rising; V _{IN BIAS} slew	UVLOHYS = 0b		200		mV
.,	Therefore also	rate < 30 V/s	UVLOHYS = 1b		400		mV
V _{UVLO}	Hysteresis	Supply rising; V _{IN BIAS} slew	UVLOHYS = 0b		0		mV
VIN_BIAS VUVLO VUVLO VUVLO VUVLO VSYS_BU VSYS_BU VINT_LDO VINT_LDO OUT LIMIT COUT COUT COUT VIN_DCDC1		rate > 30 V/s	UVLOHYS = 1b		0		mV
VIN_BIAS VUVLO VUVLO VUVLO SYS_BU VSYS_BU INT_LDO VINT_LDO OUT LIMIT COUT DCDC1 (1.1	Deglitch time				5		ms
I _{OFF}	OFF state current, total current into IN_BIAS, IN_DCDCx, IN_LDO1, IN_LSx, IN_BU	V _{IN} = 3.6 V; All rails disabled. T _J = 0°C to 85°C			5		μA
I _{SUSPEND}	SUSPEND current, total current into IN_BIAS, IN_DCDCx, IN_LDO1, IN_LSx, IN_BU	V _{IN} = 3.6 V; DCDC3 enabled, I load. All other rails disabled. T _J = 0°C to 105°C		220		μA	
SYS_BU							
	SYS_BU voltage range	Powered from V _{IN_BU} or V _{CC}		2.2		5.5	V
_	Recommended SYS_BU capacitor	Ceramic, X5R or X7R, see Table 8-3.			1		μF
OS13_BU	Tolerance	Ceramic, X5R or X7R, rated vo	-20%		20%		
INT_LDO		<u></u>					
	Output voltage				2.5		V
V_{INT_LDO}	DC accuracy	I _{OUT} < 10 mA		-2%		2%	
I _{OUT}	Output current range	Maximum allowable external lo	pad	0		10	mA
I _{LIMIT}	Short circuit current limit	Output shorted to GND			23		mA
^t HOLD	Hold-up time	All rails enabled before power	Measured from V_{INT_LDO} = 2.5 V to V_{INT_LDO} = 1.8 V All rails enabled before power off, V_{IN_BIAS} = 2.8 V to 0 V in < 1 μ s No external load on INT_LDO				ms
	Nominal output capacitor value	Ceramic, X5R or X7R, see Tab	ole 8-3.	0.1	1	22	μF
COUT	Tolerance	Ceramic, X5R or X7R, rated vo	oltage ≥ 6.3 V	-20%		20%	
DCDC1 (1.1	-V BUCK)		,				
V _{IN_DCDC1}	Input voltage range	V _{IN_BIAS} > V _{UVLO}		2.7		5.5	V
	Output voltage range	Adjustable through I ² C		0.85		1.675	V
	DC accuracy	2.7 V ≤ V _{IN} ≤ 5.5 V; 0 A ≤ I _{OUT}	≤ 1.8 A	-2%		2%	
V _{DCDC1}	Dynamic accuracy	In respect to nominal output voltage $I_{OUT} = 50$ mA to 450 mA in < 1 μ s $C_{OUT} \ge 10$ μ F, over full input voltage range.		-2.5%		2.5%	
I _{OUT}	Continuous output current	V _{IN_DCDC1} > 2.7 V				1.8	Α
IQ	Quiescent current	Total current from I _{N_DCDC1} pin no load	; Device not switching,		25	50	μA
D	High-side FET on resistance	V _{IN_DCDC1} = 3.6 V			230	5.5 20% 2% 10 22 20% 5.5 1.675 2% 2.5% 1.8	
R _{DS(ON)}	Low-side FET on resistance	V _{IN DCDC1} = 3.6 V			90	1/15	mΩ

Over operating free-air temperature range (unless otherwise noted).

	PARAMETER	TEST COI	NDITIONS	MIN	TYP	MAX	UNIT
	High-side current limit	V _{IN DCDC1} = 3.6 V			2.8		
I _{LIMIT}	Low-side current limit				3.1		A
		-	STRICT = 0b	88.5%	90%	91.5%	
	Power-good threshold	V _{OUT} falling	STRICT = 1b	95%	96.5%	96%	
			STRICT = 0b	3.8%	4.1%	4.4%	
	Hysteresis	V _{OUT} rising	STRICT = 1b		0.25%	2.8 3.1 90% 91.5% 96.5% 96% 4.1% 4.4% 9.25% 1 50 10 10 5 104% 9.25% 50 250 350 1.5 2.2 30% 22 100(8) 25 1.675 2% 1.8 25 50 230 355 90 145 2.8 3.1 90% 91.5% 96% 4.1% 4.4% 9.25% 1 50 10 10 5 10 10 5 104%	ms
V_{PG}) (C III	STRICT = 0b		1		ms
	D and State	V _{OUT} falling	STRICT = 1b		50		μs
	Deglitch	V sining	STRICT = 0b		10		μs
		V _{OUT} rising	STRICT = 1b		10		μs
	Time-out				5		ms
	Overvoltage Detection Threshold	V _{OUT} rising, STRICT = 1b		103%		104%	
V_{OV}	Hystersis	V _{OUT} falling, STRICT = 1b			0.25%		
	Deglitch	V _{OUT} rising, STRICT = 1b		-	50		μs
I _{INRUSH}	Inrush current	V _{IN_DCDC1} = 3.6 V; C _{OUT} =	10 μF to 100 μF			500	mA
R _{DIS}	Discharge resistor			150	250	350	Ω
	Nominal inductor value	Vin_DCDC1 = 3.6 V STRICT = 0b 88.5% 90% 91.5% Vour falling STRICT = 0b 3.8% 4.1% 4.4% Vour falling STRICT = 1b 95% 96.5% 96% Vour falling STRICT = 1b 95% 96.5% 96% Vour falling STRICT = 1b 0.25% ms Vour falling STRICT = 1b 50 µs Vour fising STRICT = 1b 10 µs Vour fising, STRICT = 1b 103% 104% Vour falling, STRICT = 1b 50 µs Vour falling, STRICT = 1b 50 µs Vour falling, STRICT = 1b 103% 104% Vour falling, STRICT = 1b 50 µs Vin_DCDC1 = 3.6 V; Cout = 10 µF to 100 µF 500 mA Strict = 1b 150 250 350 Ω e See Table 8-2. 1 1.5 2.2 µH alue Ceramic, X5R or X7R, see Table 8-3. 10 22 100/8 µF Vin_BIAS > Vuvlo 2.7 5.5 V Adjustable through ² C 0.85 1.675 V Adjustable through ² C 0.85 1.675 V Total current from _{N_DCDC2} pin; device not switching, no load 25 50 µA stance Vin_DCDC2 = 3.6 V 230 355 90 Vin_DCDC2 = 3.6 V 2.8 X 90 91.5% Strict = 1b 95% 95.5% 96% Vour falling STRICT = 0b 3.8% 4.1% 4.4% Vour falling STRICT = 0b 3.8% 4.1% 4.4% Vour falling STRICT = 1b 50 µs STRICT = 1b	μH				
C _{OUT}	Tolerance		-30%		30%		
C _{OUT}	Output capacitance value	Ceramic, X5R or X7R, see	Table 8-3.	10	22	100 ⁽⁸⁾	μF
DCDC2 (1.	1-V BUCK)						
V _{IN_DCDC2}			2.7		5.5	V	
V _{DCDC2}	Output voltage range	Adjustable through I ² C	0.85		1.675	V	
	DC accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V}; 0 \text{ A} \le \text{I}$	-2%		2%		
I _{OUT}	Continuous output current	V _{IN_DCDC2} > 2.7 V				1.8	Α
IQ	Quiescent current		pin; device not switching,		25	50	μA
Б.	High-side FET on resistance	V _{IN_DCDC2} = 3.6 V			230	355	
R _{DS(ON)}	Low-side FET on resistance	V _{IN_DCDC2} = 3.6 V			90	145	mΩ
	High-side current limit	V _{IN_DCDC2} = 3.6 V			2.8		
LIMIT	Low-side current limit	V _{IN_DCDC2} = 3.6 V			3.1		A
	Dawan was disharashad	V falling	STRICT = 0b	88.5%	90%	91.5%	
	Power-good threshold	V _{OUT} railing	STRICT = 1b	95%	95.5%	96%	
	Lhustanasia	V sining	STRICT = 0b	3.8%	2.8 3.1 88.5% 90% 91.8 95% 96.5% 96 3.8% 4.1% 4.4 0.25% 10 10 10 10 5 103% 104 0.25% 50 150 250 3 1 1.5 3 -30% 30 10 22 100 2.7 3 0.85 1.6 -2% 25 230 3 90 1 2.8 3.1 88.5% 90% 91.8 95% 95.5% 96 3.8% 4.1% 4.4 0.25% 10 10 10 10 10 10 10 10 10 5	4.4%	
	Hysteresis	V _{OUT} rising	STRICT = 1b		0.25%		ms
V_{PG}		\/	STRICT = 0b		1		ms
	Daniitah	V _{OUT} railing	STRICT = 1b		50		μs
	Deglitch	V sining	STRICT = 0b		10		μs
		V _{OUT} rising	STRICT = 1b		10		μs
	Time-out				5		ms
	Overvoltage Detection Threshold	V _{OUT} rising, STRICT = 1b		103%		104%	
R _{DIS} L C _{OUT} DCDC2 (1. V _{IN_DCDC2} V _{DCDC2} I _{OUT} I _Q R _{DS(ON)} I _{LIMIT}	Hystersis	V _{OUT} falling, STRICT = 1b			0.25%		
	Deglitch	V _{OUT} rising, STRICT = 1b			50		μs
I _{INRUSH}	Inrush current	V _{IN DCDC2} = 3.6 V; C _{OUT} =	10 μF to 100 μF			500	mA



Over operating free-air temperature range (unless otherwise noted).

	PARAMETER	TEST CON	DITIONS	MIN	TYP	MAX	UNIT
R _{DIS}	Discharge resistor			150	250	350	Ω
	Nominal inductor value	See Table 8-2.		1	1.5	2.2	μH
L	Tolerance			-30%		30%	
C _{OUT}	Output capacitance value	Ceramic, X5R or X7R, see	Table 8-3.	10	22	100(8)	μF
DCDC3 (1.2	-V BUCK)						
V _{IN_DCDC3}	Input voltage range	V _{IN BIAS} > V _{UVLO}				5.5	V
	Output voltage range	Adjustable through I ² C		0.9		3.4	V
V _{DCDC3}	DC accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V}; 0 \text{ A} \le \text{I}_{\text{C}}$ $\text{V}_{\text{IN}} \text{ DCDC3} \ge (\text{V}_{\text{DCDC3}} + 700)$	_{UT} ≤ 1.8 A, mV)	-2%		2%	
I _{OUT}	Continuous output current	V _{IN DCDC3} > 2.7 3.6 V			,	1.8	Α
IQ	Quiescent current	Total current from IN_DCDC Device not switching, no loa			25	50	μA
_	High-side FET on resistance	V _{IN DCDC3} = 3.6 V			230	345	
R _{DS(ON)}	Low-side FET on resistance	V _{IN DCDC3} = 3.6 V			100	150	mΩ
	High-side current limit	V _{IN DCDC3} = 3.6 V			2.8		
I _{LIMIT}	Low-side current limit	V _{IN DCDC3} = 3.6 V			3		Α
		_	STRICT = 0b	88.5%	90%	91.5%	
	Power-good threshold	V _{OUT} falling	STRICT = 1b	95%	95.5%	96%	
V_{PG}	I have to an all a		STRICT = 0b	3.8%	4.1%	4.4%	
	Hysteresis	V _{OUT} rising	STRICT = 1b		0.25%	2.2 30% 100 ⁽⁸⁾ 5.5 3.4 2% 1.8 50 345 150 91.5% 96% 4.4% 4.4% 500 3.45 105% 96% 4.4% 105% 500 3.50 2.2 30% 100	ms
V_{PG}			STRICT = 0b		1		ms
V_{PG}		V _{OUT} falling	STRICT = 1b		50		μs
	Deglitch	M. setaturu	STRICT = 0b		10		μs
		V _{OUT} rising	STRICT = 1b		10		μs
	Time-out				5	3.4 2% 1.8 50 345 150 91.5% 96% 4.4% 105% 500 350 2.2 30% 100	ms
	Overvoltage Detection Threshold	V _{OUT} rising, STRICT = 1b		104%	104.5%	105%	
V_{OV}	Hystersis	V _{OUT} falling, STRICT = 1b			0.25%		
	Deglitch	V _{OUT} rising, STRICT = 1b			50		μs
I _{INRUSH}	Inrush current	V _{IN DCDC3} = 3.6 V; C _{OUT} = 1	0 μF to 100 μF			500	mA
R _{DIS}	Discharge resistor	_		150	250	350	Ω
	Nominal inductor value	See Table 8-2.		1.0	1.5	2.2	μH
L	Tolerance			-30%		30%	
C _{OUT}	Output capacitance value	Ceramic, X5R or X7R, see	Table 8-3.	10	22	100	μF
DCDC4 (3.3	-V BUCK-BOOST) / ANALOG AI	ND I/O					
	Input voltage soft-start range	V _{IN_BIAS} > V _{UVLO} , -40°C to	+55°C	3.4			V
V_{IN_DCDC4}	input voitage soit-start range	$V_{IN_BIAS} > V_{UVLO}$, 56°C to 1	05°C	3.8		105% 500 350 2.2 30% 100 5.5 3.4	, v
	Input voltage operating range	V _{IN_BIAS} > V _{UVLO} , -40°C to	+105°C	2.7		5.5	V
R _{DIS} L C _{OUT} DCDC4 (3.	Output voltage range	Adjustable through I ² C		1.175		3.4	V
V _{DCDC4}	DC accuracy	$2.7 \text{ V} \le \text{V}_{\text{IN}} \le 5.5 \text{ V};$ $0 \text{ A} \le \text{I}_{\text{OUT}} \le 1 \text{ A}$		-2%		2%	
	Output voltage ripple	PFM mode enabled; $4.2 \text{ V} \leq \text{V}_{\text{IN}} \leq 5.5 \text{ V};$ $0 \text{ A} \leq \text{I}_{\text{OUT}} \leq 1 \text{ A} 1.6 \text{ A}$ $C_{\text{OUT}} = 80 \mu\text{F}$ $V_{\text{OUT}} = 3.3 \text{ V}$				200	mV _{pp}

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Over operating free-air temperature range PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
	Minimum duty cycle in step- down mode					18%	
		V _{IN_DCDC4} = 2.8 V, V _{OUT} = 3.3 V				1	
I _{OUT}	Continuous output current	V _{IN_DCDC4} = 3.6 V, V _{OUT} = 3				1.3	Α
		V _{IN DCDC4} = 5 V, V _{OUT} = 3.				1.6	
IQ	Quiescent current	Total current from IN_DCD switching, no load.	C4 pin; Device not		25	50	μA
f _{SW}	Switching frequency				2400		kHz
			IN_DCDC4 to L4A		166		
_	High-side FET on resistance	$V_{IN_DCDC3} = 3.6 V$	L4B to DCDC4		149		
R _{DS(ON)}	Lauraida FFT an maistanas	- 2 C V	L4A to GND		142	190	mΩ
	Low-side FET on resistance	$V_{IN_DCDC3} = 3.6 V$	L4B to GND	,	144	190	
I _{LIMIT}	Average switch current limit	V _{IN DCDC4} = 3.6 V	'		3000		mA
	D 141 1 11	- C III	STRICT = 0b	88.5%	90%	91.5%	
	Power-good threshold	V _{OUT} falling	STRICT = 1b	95%	96.5%	96%	
		.,	STRICT = 0b	3.8%	4.1%	4.4%	
	Hysteresis	V _{OUT} rising	STRICT = 1b		0.25%		ms
V_{PG}			STRICT = 0b		1		ms
		V _{OUT} falling	STRICT = 1b		50		μs
	Deglitch	V riging	STRICT = 0b		10		μs
		V _{OUT} rising	STRICT = 1b		10		μs
	Time-out				5		ms
	Overvoltage Detection Threshold	V _{OUT} rising, STRICT = 1b		103%		104%	
V _{OV}	Hystersis	V _{OUT} falling, STRICT = 1b			0.25%		
	Deglitch	V _{OUT} rising, STRICT = 1b			50		μs
I _{INRUSH}	Inrush current	V _{IN DCDC4} = 3.6 V; C _{OUT} =	10 μF to 100 μF			500	mA
R _{DIS}	Discharge resistor	_		150	250	350	Ω
	Nominal inductor value	See Table 8-2.		1.2	1.5	2.2	μH
L	Tolerance			-30%		30%	
C _{OUT}	Output capacitance value	Ceramic, X5R or X7R, see	Table 8-3.	40	80	100	μF
	d DCDC6 (POWER PATH)						
V _{CC}	DCDC5 and DCDC6 input voltage range.	V _{IN_BU} = 0 V		2.2		3.3	V
V _{IN_BU}	DCDC5 and DCDC6 input voltage range ⁽¹⁾			2.2		5.5	V
t _{RISE}	V _{CC} , V _{IN_BU} rise time	V _{CC} = 0 V to 3.3 V, V _{IN_BU}	= 0 V to 5.5 V	30			μs
Б	Power path switch impedance	CC to SYS_BU V _{CC} = 2.4 V, V _{IN_BU} = 0 V			14.5		0
R _{DS(ON)}	Power path switch impedance	IN_BU to SYS_BU V _{IN_BU} = 3.6 V			10.5		Ω
I _{LEAK}	Forward leakage current	Into CC pin; V _{CC} = 3.3 V, V _{IN_BU} = 0 V; OFF state; FSEĀL = 0b; over full temperature range)		50	300	nA
	Reverse leakage current	Out of CC pin; V _{CC} = 1.5 V; V _{IN_BU} = 5.5 \ over full temperature range			500		



Over operating free-air temperature range (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
R _{CC}	Acceptable CC source impedance	Source I _{OUT, DCDC5} < 10 μA; I _{OUT, DCDC6} < 10 μA			1000	Ω
IQ	Quiescent current	Average current into CC pin; RECOVERY or POWER_OFF state; V_{IN_BU} = 0 V; V_{CC} = 2.4 V; DCDC5 and DCDC6 enabled, no load T_J = 25°C		350		nA
DCDC5 (1-	V BATTERY BACKUP SUPPLY)					
	Output voltage			1		V
		2.7 V≤V _{IN_BU} ≤ 5.5 V; 1.5 μA≤I _{OUT} ≤25 mA−40°C≤TA< 0°C	-2.5%		2.5%	
V_{DCDC5}	DC accuracy	2.7 V≤V _{IN_BU} ≤5.5 V 1.5 μA≤ I _{OUT} ≤25 mA 0°C≤TA< 105°C	-2%		2%	
		2.2 V≤V _{CC} ≤3.3 V; V _{IN_BU} = 0;1.5 μA ≤ I _{OUT} ≤100 μA	-2.5%		2.5%	
	Output voltage ripple	L = 10 μH; C _{OUT} = 22 μF; 100-μA load, occurs during band-gap sampling			32	mV _{pp}
I _{OUT}	Continuous output current	$2.2 \text{ V} \le \text{V}_{\text{CC}} \le 3.3 \text{ V}$ $\text{V}_{\text{IN_BU}} = 0 \text{ V}$		10	100	μA
	·	2.7 V ≤ V _{IN_BU} ≤ 5.5 V			25	mA
I _{LIMIT}	High-side current limit	V _{IN_BU} = 2.8 V	,	50		mA
W	Power-good threshold	V _{OUT} falling	79%	85%	91%	
V_{PG}	Hysteresis	V _{OUT} rising		6%		
	Nominal inductor value	Chip inductor, see Table 8-3.	4.7	10	22	μH
L	Tolerance		-30%		30%	
_	Output capacitance value	Ceramic, X5R or X7R, see Table 8-3.	20		47	μF
C _{OUT}	Tolerance		-20%		20%	-
DCDC6 (1.	8-V BATTERY BACKUP SUPPLY	7)				
	Output voltage			1.8		V
	-	2.7 V ≤ V _{IN BU} ≤ 5.5 V;	20/		20/	
V_{DCDC6}	DC accuracy	1 μA ≤ I _{OUT} ≤ 25 mA	-2%		2%	
	Do accuracy	2.2 V≤V _{CC} ≤ 3.3 V, V _{IN_BU} = 0; 1 µA ≤ I _{OUT} ≤100 µA	-2%		2%	
		2.2 V ≤ V _{CC} ≤ 3.3 V		10	100	μA
I _{OUT}	Continuous output current	V _{IN_BU} = 0 V				'
	T	2.7 V ≤ V _{IN_BU} ≤ 5.5 V			25	mA
R _{DS(ON)}	High-side FET on resistance	V _{IN_BU} = 3 V		2.5	3.5	Ω
_	Low-side FET on resistance	V _{IN_BU} = 3 V		2	3	_
I _{LIMIT}	High-side current limit	V _{IN_BU} = 3 V	,	50		mA
V _{PG}	Hysteresis	V _{OUT} rising		3%		
L	Nominal inductor value	Chip inductor, see Table 8-3	4.7	10	22	μH
	Tolerance		-30%		30%	
C _{OUT}	Output capacitance value	Ceramic, X5R or X7R, see Table 8-3	20		47	μF
	Tolerance		-20%		20%	
LDO1 (1.8	-V LDO)					
V _{IN_LDO1}	Input voltage range	$V_{IN_BIAS} > V_{UVLO}$	1.8		5.5	V
lQ	Quiescent current	No load		35		μΑ
V _{OUT}	Output voltage range	Adjustable through I ² C	0.9		3.4	V
• 001	DC accuracy	$V_{OUT} + 0.2 \text{ V} \le V_{IN} \le 5.5 \text{ V}; 0 \text{ A} \le I_{OUT} \le 200 \text{ mA}$	-2%		2%	

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<u> </u>	e (unless otherwise noted).					
PARAMETER	TEST CONDITIONS			TYP		UNIT
Output current range	_		0		200	mA
	V _{IN_LDO1} > 2.7 V, V _{OUT} = 1.8 V		0		400	
Short circuit current limit	Output shorted to GND		445	550		mA
Dropout voltage	I _{OUT} = 100 mA, V _{IN} = 3.6 V				200	mV
Power-good threshold	Vour falling	STRICT = 0b	88.5%	90%	91.5%	
Tower good amounted	V ₀₀₁ raiming	STRICT = 1b	95%	96.5%	96%	
Hysteresis	Vour rising	STRICT = 0b	3.8%	4.1%	4.4%	
Tryotoroolo	V ₀₀₁ rising	STRICT = 1b		0.25%		ms
	Vour falling	STRICT = 0b		1		ms
Dealitch	V ₀₀₁ raming	STRICT = 1b		50		μs
Degitori	Vous rising	STRICT = 0b		10		μs
	VOUL Hairid	STRICT = 1b		10		μs
Time-out				5		ms
Overvoltage Detection Threshold	V _{OUT} rising, STRICT = 1b		103%		104%	
Hystersis	V _{OUT} falling, STRICT = 1b			0.25%		
Deglitch	V _{OUT} rising, STRICT = 1b			50		μs
Inrush current	V _{IN_DCDC2} = 3.6 V; C _{OUT} = 10 μF to 100 μF				500	mA
Discharge resistor			150	250	350	Ω
Nominal output Output capacitance value	Ceramic, X5R or X7R		10		100	μF
TCH 1 (LS1)		,				
Input voltage range	V _{IN_BIAS} > V _{UVLO}		1.2		3.6	V
	V_{IN_LS1} = 3.3 V, I_{OUT} = 300 mA, over full temperature range				110	
	V _{IN_LS1} = 1.8 V, I _{OUT} = 300 mA, DDR2, LPDDR, MDDR at 266 MHz over full temperature range				110	
Static on resistance	V _{IN_LS1} = 1.5 V, I _{OUT} = 300 mA, DDR3 at 333 MHz over full temperature range V _{IN_LS1} = 1.35 V, I _{OUT} = 300 mA, DDR3L at 333 MHz over full temperature range V _{IN_LS1} = 1.2 V, I _{OUT} = 200 mA, LPDDR2 at 333 MHz over full temperature range				110	mΩ
					110	
					150	
Short circuit current limit	Output shorted to GND		350			mA
Overtemperature shutdown ⁽³⁾			125	132	139	°C
Hysteresis				10		
Nominal output capacitance value	Ceramic, X5R or X7R, see Table 8-3.		10		100	μF
TCH 2 (LS2)	•	-				
Input voltage range	V _{IN_BIAS} > V _{UVLO}		4		5.5	V
Undervoltage lockout		falling ⁽⁴⁾	2.48	2.6	2.7	V
Hysteresis	Input voltage rising			170		mV
Static on resistance	V_{IN_LS2} = 5 V, I_{OUT} = 500 mA, range	over full temperature			500	mΩ
	PARAMETER Output current range Short circuit current limit Dropout voltage Power-good threshold Hysteresis Deglitch Time-out Overvoltage Detection Threshold Hystersis Deglitch Inrush current Discharge resistor Nominal output Output capacitance value TCH 1 (LS1) Input voltage range Short circuit current limit Overtemperature shutdown(3) Hysteresis Nominal output capacitance value TCH 2 (LS2) Input voltage range Undervoltage lockout Hysteresis	Dutput current range	Dutput current range	PARAMETER	PARAMETER TEST CONDITIONS MIN TYP Output current range V _{IN_LDO1} - V _{DO} = Vout 0 0 Short circuit current limit Output shorted to GND 445 550 Dropout voltage I _{OUT} = 100 mA, V _{IN} = 3.6 V STRICT = 0b 88.5% 90% Power-good threshold Vour falling STRICT = 0b 3.8% 4.1% Hysteresis Vour falling STRICT = 0b 3.8% 4.1% STRICT = 1b 0.25% 5TRICT = 1b 0.25% Time-out STRICT = 0b 1 1 Overvoltage Detection Threshold 10 5TRICT = 1b 10 Hystersis Vour falling, STRICT = 1b 103% 10 Hystersis Vour falling, STRICT = 1b 0.25% 10 Deglitch Vour falling, STRICT = 1b 10	TEST CONDITIONS MIN TYP MAX Output current range VIN_LDO1 > 2.7 V, Vour = 1.8 V 0 200 Short circuit current limit Output shorted to GND 445 550 Dropout voltage IouT = 100 mA, V _N = 3.8 V 200 Power-good threshold Vour falling STRICT = 0b 88.5% 90% 91.5% Hysteresis Vour falling STRICT = 0b 3.8% 4.1% 4.4% Fried = 0b 1 0.25% STRICT = 1b 95% 96.5% 96% Deglitch Vour falling STRICT = 0b 1 0.25% 5TRICT = 1b 10 10 Time-out STRICT = 1b 50 5TRICT = 1b 10<



Over operating free-air temperature range (unless otherwise noted).

PARAMETER		TEST CONDIT	TEST CONDITIONS		TYP	MAX	UNIT
			LS2ILIM[1:0] = 00b	94		126	
		Output shorted to GND; V _{IN LS2}	LS2ILIM[1:0] = 01b	188		251	mA
I _{LIMIT}	Short circuit current limit	≥ 4 V	LS2ILIM[1:0] = 10b	465		631	
			LS2ILIM[1:0] = 11b	922		1290	
I _{LEAK}	Reverse leakage current	V _{LS2} > V _{IN_LS2} + 1 V			12	30	μA
t _{BLANK}	Interrupt blanking time	Output shorted to GND until inte	errupt is triggered		15		ms
R _{DIS}	Internal discharge resistor at output ⁽²⁾	LS2DCHRG = 1b		150	250	380	Ω
-	Overtemperature shutdown ⁽⁴⁾			125	132	139	°C
T _{OTS}	Hysteresis			-	10		
C _{OUT}	Nominal output capacitance value	Ceramic, X5R or X7R, see Table	e 8-3.	1		100	μF
LOAD SW	ITCH 3 (LS3)						
V _{IN_LS3}	Input voltage range	V _{IN_BIAS} > V _{UVLO}		1.8		10	V
R _{DS(ON)} St		V _{IN_LS3} = 9 V, I _{OUT} = 500 mA, ov range	er full temperature			440	
	Static on resistance	V _{IN_LS3} = 5 V, I _{OUT} = 500 mA, over full temperature range				526	mΩ
		V_{IN_LS3} = 2.8 V, I_{OUT} = 200 mA, orange			656		
		V _{IN_LS3} = 1.8 V, I _{OUT} = 200 mA, orange	over full temperature			910	
			LSILIM[1:0] = 00b	98		126	
	Short circuit current limit	Output shorted to GND	LSILIM[1:0] = 01b	194		253	mA
			LSILIM[1:0] = 10b	475		738	
I _{LIMIT}			LSILIM[1:0] = 11b	900		1234	
		V _{IN_LS} ≤ 2.3 V, Output shorted to GND	LSILIM[1:0] = 00b	98		126	
			LSILIM[1:0] = 01b	194	<u>.</u>	253	
		LSILIM[1:0] = 10b		475		738	
t _{BLANK}	Interrupt blanking time	Output shorted to GND until inte	errupt is triggered.		15		ms
R_{DIS}	Internal discharge resistor at output ⁽²⁾	LS3DCHRG = 1		650	1000	1500	Ω
T _{OTS}	Overtemperature shutdown ⁽⁴⁾			125	132	139	°C
1018	Hysteresis				10		°C
C _{OUT}	Nominal output capacitance value	Ceramic, X5R or X7R, see Table	e 8-3.	1	100	220	μF
BACKUP	BATTERY MONITOR						
		Ideal level			3		V
V_{TH}	Comparator threshold	Good level			2.6		V
- IH		Low level		2.3		V	
	Accuracy			-3%		3%	
R _{LOAD}	Load impedance	Applied from CC to GND during	comparison.	70	100	130	kΩ
t _{DLY}	Measurement delay	R _{LOAD} is connected during delaying taken at the end of delay.		600		ms	

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	PARAMETER	TEST CONDI	TIONS	MIN	TYP	MAX	UNIT
		PGDLY[1:0] = 00b			10		
PG_{DLY}	PGOOD delay time	PGDLY[1:0] = 01b			20		
		PGDLY[1:0] = 10b			50		ms
		PGDLY[1:0] = 11b			150		
		DD: 4	Rising edge		100		ms
		PB input	Falling edge		50		ms
		AC DET:	Rising edge		100		μs
		AC_DET input	Falling edge		10		ms
	Described disco	DIAID EN in mot	Rising edge		10		ms
t _{DG}	Deglitch time	PWR_EN input	Falling edge		100		μs
		ODIO4	Rising edge		1		ms
		GPIO1	Falling edge		1		ms
		ODIOS ODIOS	Rising edge		5		μs
		GPIO3 GPIO2	Falling edge		5		μs
	Decet the c	TR:	TRST = 0b		8		
^t RESET	Reset time	PB input held low TRST = 1b			15		S
		SCL, SDA, GPIO1, and GPIO3 GPIO2		1.3	-		
V _{IH} High	High level input voltage	AC_DET, PB		0.66 × IN_BIAS			V
		PWR_EN		1.3			
V _{IL}	Low level input voltage	SCL, SDA, PWR_EN, AC_DET, PB, GPIO1, and GPIO3 GPIO2		0		0.4	V
V	High level autout valte as	GPO2; I _{SOURCE} = 5 mA; GPO2_BUF = 1		V _{IN_LS1} - 0.3		V _{IN_LS1}	
V_{OH}	High level output voltage	PGOOD_BU; I _{SOURCE} = 100 μA		V _{DCDC6} – 10 mV			V
		nWAKEUP, nINT, SDA, PGOOD, GPIO1, GPO2, and GPIO3; I _{SINK} = 2 mA		0		0.3	\ \ \
V_{OL}	Low level output voltage	nPFO; I _{SINK} = 2 mA		0		0.35	
		PGOOD_BU; I _{SINK} = 100 μA		0		0.3	
	Power-fail comparator threshold	Input falling			800		mV
	Hysteresis	Input rising			40		mV
V_{PFI}	Accuracy		·	-4%		4%	
	Deglitch	Input falling			25		μs
	Degillon	Input rising			10		ms
I _{DC34_SEL}	DC34_SEL bias current	Enabled only at power-up.			10		μA
		Threshold 1			100		
		Threshold 2			163		
	D0D00 4 D0D04	Threshold 3			275		
V_{DC34_SEL}	DCDC3 and DCDC4 power-up default selection thresholds	Threshold 4			400		mV
		Threshold 5			575		
		Threshold 6			825		
		Threshold 7			1200		



Over operating free-air temperature range (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
		Setting 0	0	0	7.7	
		Setting 1	11.3	12.1	13	
		Setting 2	18.1	20	22	
D	DCDC3 and DCDC4 power-up	Setting 3	30.9	31.6	32.3	kΩ
R _{DC34_SEL}	default selection resistor values	Setting 4	44.8	45.3	46.4	K22
		Setting 5	64.2	64.9		
		Setting 6	92.9	95.3	96.9	
		Setting 7	135.3	150		
I _{BIAS} II	Input bias current	SCL, SDA, GPIO1 ⁽⁵⁾ , GPIO3 ⁽⁵⁾ ; V _{IN} = 3.3 V		0.01	1	μΑ
	input bias current	PB, AC_DET, PFI; V _{IN} = 3.3 V			500	nA
I _{LEAK}	Pin leakage current	nINT, nWAKEUP, nPFO, PGOOD, PWR_EN, GPIO1 ⁽⁶⁾ , GPO2 ⁽⁷⁾ , GPIO3 ⁽⁶⁾ V _{OUT} = 3.3 V			500	nA
OSCILLATO	OR		<u> </u>			
£	Oscillator frequency			2400		kHz
fosc	Frequency accuracy	$T_J = -40^{\circ}\text{C to } +105^{\circ}\text{C}$	-12%	-	12%	
OVERTEM	PERATURE SHUTDOWN			-		
т	Overtemperature shutdown	Increasing junction temperature	135	145	155	°C
T _{OTS}	Hysteresis	Decreasing junction temperature		20		
т	High-temperature warning	Increasing junction temperature	90	100	110	°C
T _{WARN}	Hysteresis	Decreasing junction temperature		15		

- IN_BU has priority over CC input.
- (2)
- Discharge function disabled by default.

 Switch is temporarily turned OFF if temperature exceeds OTS threshold.

 Switch is temporarily turned OFF if input voltage drops below UVLO threshold. (3) (4) (5)
- Configured as input.
- Configured as output. (6)
- (7) Configured as open-drain output.
- 500-μF of remote capacitance can be supported for DCDC1 and DCDC2.

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6.6 Timing Requirements

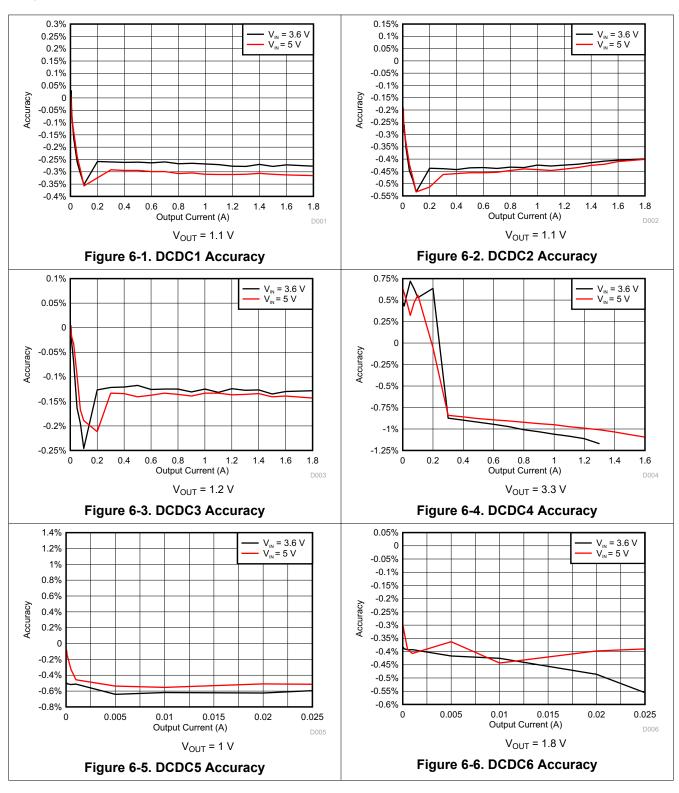
			MIN	NOM	MAX	UNIT
f	Social clock froguency			100		kHz
f _{SCL}	Serial clock frequency			400		KΠZ
	Hold time (repeated) START condition. After this period, the	SCL = 100 kHz	4			μs
t _{HD;STA}	first clock pulse is generated.	SCL = 400 kHz	600			ns
	LOW period of the SCL clock	SCL = 100 kHz	4.7			
t _{LOW}	LOW period of the SCL clock	SCL = 400 kHz	1.3			μs
	LUCII paried of the CCI plant	SCL = 100 kHz	4			
t _{HIGH}	HIGH period of the SCL clock	SCL = 400 kHz ⁽¹⁾	1			μs
	Cat up time for a repeated CTART condition	SCL = 100 kHz	4.7			μs
t _{SU;STA}	Set-up time for a repeated START condition	SCL = 400 kHz	600			ns
t _{HD;DAT} Data hold t	Data hald time	SCL = 100 kHz	0		3.45	μs
	Data noid time	SCL = 400 kHz	0		900	ns
. 5	Data act up time	SCL = 100 kHz	250			
SU;DAT	Data set-up time	SCL = 400 kHz	100			ns
	Dies time of both CDA and CCI signals	SCL = 100 kHz			1000	
t _r	Rise time of both SDA and SCL signals	SCL = 400 kHz			300	ns
	Fall time of both SDA and SCL signals	SCL = 100 kHz			300	no
t _f	Fall time of both SDA and SCL signals	SCL = 400 kHz			300	ns
	Cat up time for CTOD condition	SCL = 100 kHz	4			μs
t _{SU;STO}	Set-up time for STOP condition	SCL = 400 kHz	600			ns
	Bus free time between STOP and START condition	SCL = 100 kHz	4.7			
BUF	DUSTIFE LITTLE DELWEET STOP AND START CONDITION	SCL = 400 kHz	1.3			μs
	Pulse width of spikes which must be suppressed by the input	SCL = 100 kHz	(2)		(2)	nc
t _{SP}	filter	SCL = 400 kHz	0		50	ns
	Conscitive load for each bug line	SCL = 100 kHz			400	"F
C _b	Capacitive load for each bus line	SCL = 400 kHz			400	pF

The SCL duty cycle at 400 kHz must be > 40%. The inputs of $\rm I^2C$ devices in Standard-mode do not require spike suppression. (1) (2)



6.7 Typical Characteristics

At $T_J = 25$ °C unless otherwise noted.



7 Detailed Description

7.1 Overview

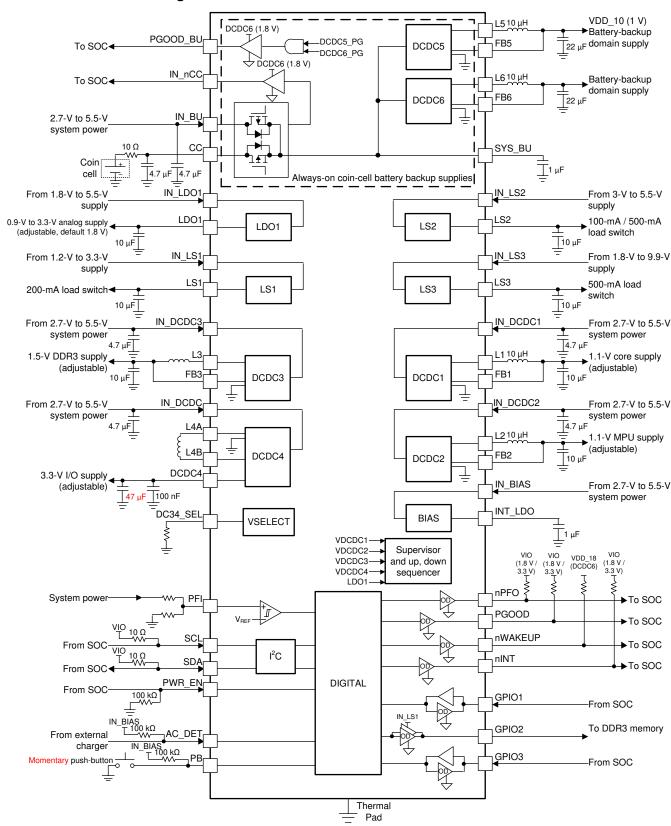
The TPS6521845 provides three step-down converters, three load switches, three general-purpose I/Os, two battery backup supplies, one buck-boost converter, and one LDO. The system can be supplied by a regulated 5-V supply. The device is characterized across a –40°C to +105°C temperature range, which makes it suitable for various industrial applications.

The I^2C interface provides comprehensive features for using TPS6521845. All rails, load switches, and GPIOs can be enabled and disabled. Voltage thresholds for the UVLO and supervisor can be customized. Power-up and power-down sequences can also be programmed through I^2C . Interrupts for overtemperature, overcurrent, and undervoltage can be monitored for the load-switch.

The three hysteretic step-down converters can each supply up to 1.8 A of current. The default output voltages for each converter can be adjusted through the I²C interface. DCDC1 and DCDC2 features dynamic voltage scaling with an adjustable slew rate. The step-down converters operate in a low power mode at light load, and can be forced into power mode (PWM) operation for noise sensitive applications.



7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Wake-Up and Power-Up and Power-Down Sequencing

The TPS6521845 has a predefined power-up and power-down sequence, which does not change in a typical application. The user can define custom sequences with I^2C . The power-up sequence is defined by a series of ten strobes and nine delay times. Each output rail is assigned to a strobe to determine the order of enabling rails. A single rail is assigned to only one strobe, but multiple rails can be assigned to the same strobe. The delay times between strobes are between 2 ms and 5 ms.

7.3.1.1 Power-Up Sequencing

When the power-up sequence initiates, STROBE 1 occurs, and any rail assigned to this strobe is enabled. After a delay time of DLY1, STROBE 2 occurs and the rail assigned to this strobe is powered up. The sequence continues until all strobes occur and all DLYx times execute. Strobe assignments and delay times are defined in the SEQx registers, and are changed under I²C control. The power-up sequence executes if one of the following events occurs:

- · From the OFF state:
 - The push-button (PB) is pressed (falling edge on PB) or
 - The AC DET pin is pulled low (falling edge) or
 - The PWR EN is asserted (driven to high-level) or
 - The main power is connected (IN BIAS) and AC DET is grounded and
 - The device is not in undervoltage lockout (UVLO) or overtemperature shutdown (OTS).
- From the PRE_OFF state:
 - The PB is pressed (falling edge on PB) or
 - The AC DET pin is pulled low (falling edge) or
 - The PWR_EN is asserted (driven to high-level) and
 - The device is not in UVLO or OTS.
- · From the SUSPEND state:
 - The PB is pressed (falling edge on PB) or
 - The AC DET pin is pulled low (falling edge) or
 - The PWR EN pin is pulled high (level sensitive) and
 - The device is not in UVLO or OTS.

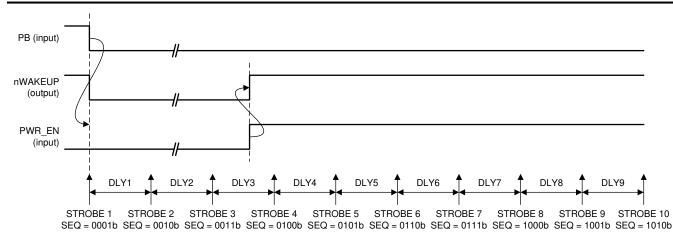
When a power-up event is detected, the device enters a WAIT_PWR_EN state and triggers the power-up sequence. The device remains in WAIT_PWR_EN as long as the PWR_EN and either the PB or AC_DET pin are held low. If both, the PB and AC_DET return to logic-high state and the PWR_EN pin has not been asserted within 20 s of entering WAIT_PWR_EN state, the power-down sequence is triggered and the device returns to OFF state. Once PWR_EN is asserted, the device advances to ACTIVE state, which is functionally equivalent to WAIT_PWR_EN. However, the AC_DET pin is ignored and power-down is controlled by the PWR_EN pin only.

Rails not assigned to a strobe (SEQ = 0000b) are not affected by power-up and power-down sequencing and remain in their current ON or OFF state regardless of the sequencer. A rail can be enabled and disabled at any time by setting the corresponding enable bit in the ENABLEx register, with the exception that the ENABLEx register cannot be accessed while the sequencer is active. Enable bits always reflect the current enable state of the rail. For example, the sequencer sets and resets the enable bits for the rails under its control.

Note

The power-up sequence is defined by strobes and delay times, and can be triggered by the PB, AC_DET (not shown, same as PB), or PWR_EN pin.





Push-button deglitch time is not shown.

Figure 7-1. Power-Up Sequences from OFF or SUSPEND State; PB is Power-Up Event

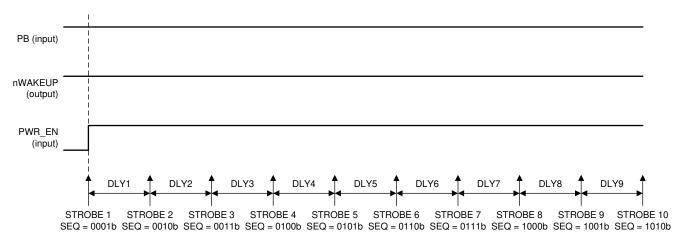


Figure 7-2. Power-Up Sequences from SUSPEND State; PWR_EN is Power-Up Event

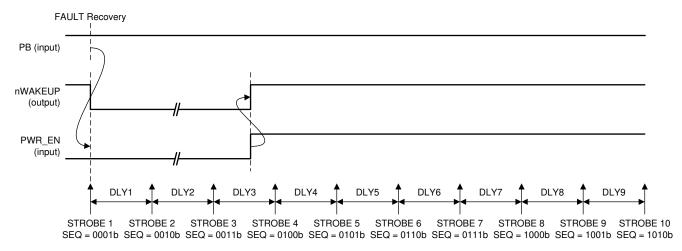


Figure 7-3. Power-Up Sequences from RECOVERY State

7.3.1.2 Power-Down Sequencing

By default, the power-down sequence follows the reverse of the power-up sequence. When the power-down sequence is triggered, STROBE 10 occurs and any rail assigned to STROBE 10 is shut down and its discharge circuit is enabled. After a delay time of DLY9, STROBE 9 occurs and any rail assigned to it is shut down and its discharge circuit is enabled. The sequence continues until all strobes occur and all DLYx times execute. The DLYx times are extended by a factor of 10x to provide ample time for discharge, and preventing output voltages from crossing during shut-down. The DLYFCTR bit is applied globally to all power-down delay times. Regardless of the DLYx and DLYFCTR settings, the PMIC enters OFF, SUSPEND, or RECOVERY state 500 ms after the power-down sequence initiates, to ensure that the discharge circuits remain enabled for a minimum of 150 ms before the next power-up sequence starts.

A power-down sequence executes if one of the following events occurs:

- The device is in the WAIT_PWR_EN state, the PB and AC_DET pins are high, PWR_EN is low, and the 20-s timer has expired.
- The device is in the ACTIVE state and the PWR EN pin is pulled low.
- The device is in the WAIT_PWR_EN, ACTIVE, or SUSPEND state and the push-button is held low for > 8 s (15 s if TRST = 1b).
- A fault occurs in the device (OTS, UVLO, PGOOD failure).

When transitioning from ACTIVE to SUSPEND state, the rails not controlled by the power-down sequencer maintains the same ON/OFF state in SUSPEND state that it had in ACTIVE state. This allows for the selected power rails to remain powered up when in the SUSPEND state.

When transitioning to the OFF or RECOVERY state, rails not under sequencer control are shut-down as follows:

- DCDC1, DCDC2, DCDC3, DCDC4, LDO1, and LS1 shut down at the beginning of the power-down sequence, if not under sequencer control (SEQ = 0b).
- LS2 and LS3 shut down as the state machine enters an OFF or RECOVERY state; 500 ms after the power-down sequence is triggered.

If the supply voltage on IN_BIAS drops below 2.5 V, the digital core is reset and all power rails are shut down instantaneously and are pulled low to ground by their internal discharge circuitry (DCDC1-4, and LDO1). The amount of time the discharge circuitry remains active is a function of the INT_LDO hold up time (see Section 7.3.1.6 for more details).

7.3.1.3 Strobe 1 and Strobe 2

STROBE 1 and STROBE 2 are dedicated to DCDC5 and DCDC6 which are *always-on*; powered up as soon as the device exits the OFF state, and ON in any other state. STROBE 1 and STROBE 2 options are available only for DCDC5 and DCDC6, not for any other rails.

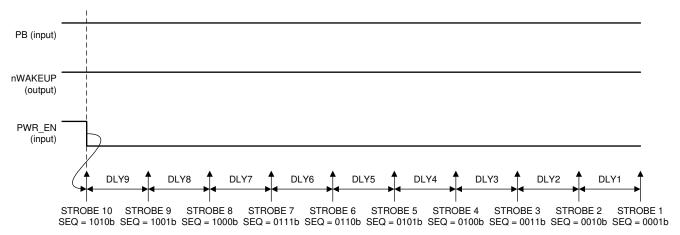
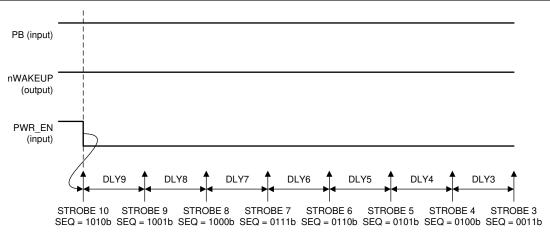


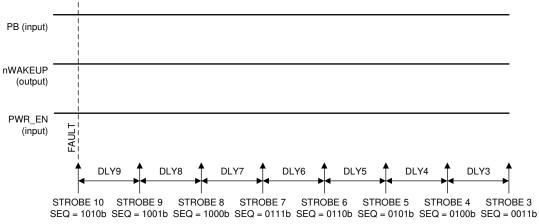
Figure 7-4. Power-Down Sequences to OFF State; PWR EN is Power-Down Event; FSEAL = 0b





STROBE2 and STROBE1 are not shown.

Figure 7-5. Power-Down Sequences to SUSPEND State; PWR_EN is Power-Down Event; FSEAL = 1b



STROBE2 and STROBE1 are not shown.

Figure 7-6. Power-Down Sequences to RECOVERY State; TSD or UV is Power-Down Event

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7.3.1.4 Supply Voltage Supervisor and Power-Good (PGOOD)

Power-good (PGOOD) is an open-drain output of the built-in voltage supervisor that monitors DCDC1, DCDC2, DCDC3, DCDC4, and LDO1. The output is Hi-Z when all enabled rails are in regulation and driven low when one or more rails encounter a fault which brings the output voltage outside the specified tolerance range. In a typical application PGOOD drives the reset signal of the SOC.

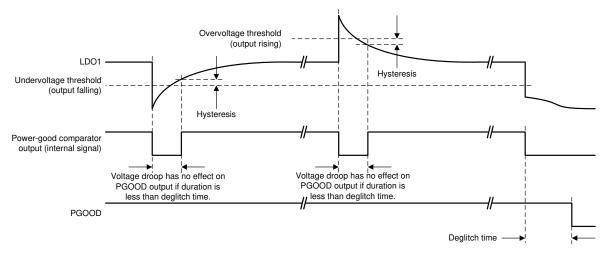


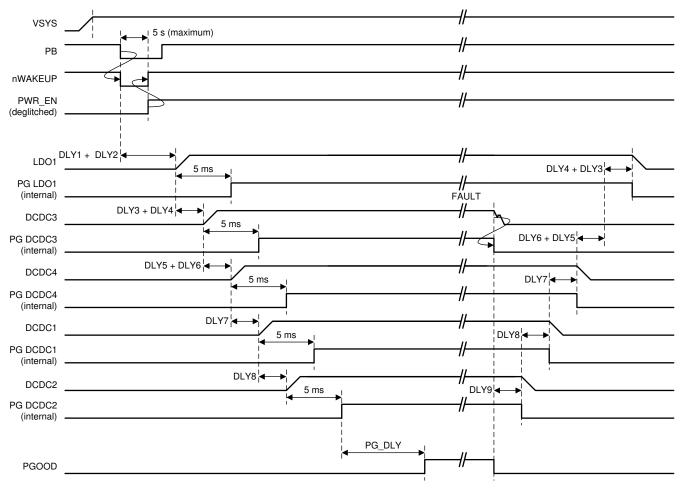
Figure 7-7. Definition of Undervoltage, Overvoltage Thresholds, Hysteresis, and Deglitch Times

The following rules apply to the PGOOD output:

- The power-up default state for THE PGOOD is low. When all rails are disabled, the PGOOD output is driven low.
- Only enabled rails are monitored. Disabled rails are ignored.
- Power-good monitoring of a particular rail starts 5 ms after the rail is enabled and is continuously monitored thereafter. This allows the rail to power-up.
- The PGOOD is delayed by PGDLY time after the sequencer is finished and the last rail is enabled.
- If an enabled rail is continuously outside the monitoring threshold for longer than the deglitch time, then the PGOOD is pulled low, and all rails are shut-down following the power-down sequence. PGDLY does not apply.
- Disabling a rail manually by resetting the DCx_EN or LDO1_EN bit has no effect on the PGOOD pin. If all rails are disabled, the PGOOD is driven low as the last rail is disabled.
- If the power-down sequencer is triggered, PGOOD is driven low.
- The PGOOD is driven low in the SUSPEND state, regardless of the number of rails that are enabled.

Figure 7-8 shows a typical power-up sequence and PGOOD timing.





A. (1) Sequence shown for TPS65218D0 variant. For other TPS65218xx variants, refer to registers SEQ1-7 in Section 5.6.4 for factory programmed sequence order and timing.

Figure 7-8. Typical Power-Up Sequence of the Main Output Rails

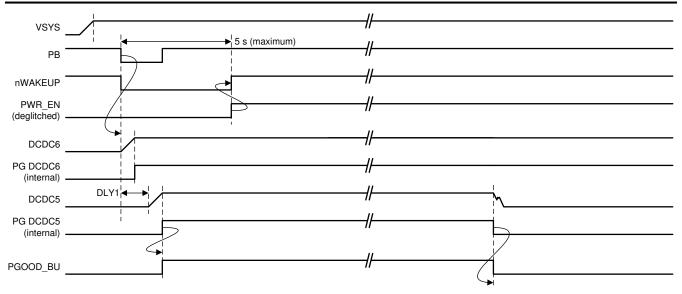
7.3.1.5 Backup Supply Power-Good (PGOOD_BU)

PGOOD_BU is a push-pull output indicating if DCDC5 and DCDC6 are in regulation. The output is driven to high when both rails are in regulation, and driven low if at least one of the rails is below the power-good threshold. The output-high level is equal to the output voltage of DCDC6.

PGOOD_BU is the logical *and* between PGOOD (DCDC5) and PGOOD (DCDC6), and has no delay time built-in. Unlike the main power-good, a fault on DCDC5 or DCDC6 does not trigger the power-down sequencer, does not disable any of the rails in the system, and has no effect on the PGOOD pin. DCDC5 and DCDC6 recover automatically once the fault is removed.

Note

In this example, the power-down is triggered by a fault on DCDC3.



A. Sequence shown for TPS65218D0 and TPS6521825 variants. For TPS6521815 variant, order and timing of DCDC5 and DCDC6 can be modified using registers SEQ1-2 and SEQ5 in Section 7.5.4.

Figure 7-9. Typical Power-Up Sequence of DCDC5 and DCDC6

7.3.1.6 Internal LDO (INT_LDO)

The internal LDO provides a regulated voltage to the internal digital core and analog circuitry. The internal LDO has a nominal output voltage of 2.5 V and can support up to 10 mA of external load.

When system power fails, the UVLO comparator triggers the power-down sequence. If system power drops below 2.5 V, the digital core is reset and all remaining power rails are shut down instantaneously and are pulled low to ground by their internal discharge circuitry (DCDC1-4 and LDO1).

The internal LDO reverse blocks to prevent the discharging of the output capacitor (C_{INT_LDO}) on the INT_LDO pin. The remaining charge on the INT_LDO output capacitor provides a supply for the power rail discharge circuitry to ensure the outputs are discharged to ground even if the system supply has failed. The amount of hold-up time specified in is a function of the output capacitor value (C_{INT_LDO}) and the amount of external load on the INT_LDO pin, if any. The design allows for enough hold-up time to sufficiently discharge DCDC1-4, and LDO1 to ensure proper processor power-down sequencing. The amount of hold-up time is a function of the output capacitor value, which should not exceed 22 μ F and the amount of external load, if any.

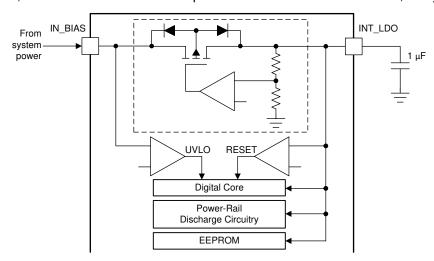


Figure 7-10. Internal LDO and UVLO Sensing

7.3.1.7 Current Limited Load Switches

The TPS6521845 provides three current limited load switches with individual inputs, outputs, and enable control. Each switch provides the following control and diagnostic features:

- The ON or OFF state of the switch is controlled by the corresponding LSx_EN bit in the ENABLE register.
- LS1 can be controlled by the sequencer or through I²C communication.
- LS2 and LS3 can *only* be controlled through I²C communication. The sequencer has no control over LS2 and LS3.
- Each switch has an active discharge function, disabled by default, and enabled through the LSxDCHRG bit. When enabled, the switch output is discharged to ground whenever the switch is disabled.
- When the PFI input drops below the power-fail threshold (the power-fail comparator trips), the load switches are automatically disabled to shed system load. This function must be individually enabled for each switch through the corresponding LSxnPFO bit. The switches do not turn back on automatically as the system voltage recovers, and must be manually re-enabled.
- An interrupt (LSx_I) issues whenever a load switch actively limits the output current, such as when the output load exceeds the current limit value. The switch remains ON and provides current to the load according to the current-limit setting.
- All three load switches have local overtemperature sensors which disable the corresponding switch if the
 power dissipation and junction temperature exceeds the safe operating value. The switch automatically
 recovers once the temperature drops below the OTS threshold value minus hysteresis. The LSx_F (fault)
 interrupt bit is set while the switch is held OFF by the OTS function.

7.3.1.7.1 Load Switch 1 (LS1)

LS1 is a non-reverse blocking, low-voltage (< 3.6 V), low-impedance switch intended to support DDRx self-refresh mode by cutting off the DDRx supply to the SOC DDRx interface during SUSPEND mode. In a typical application, the input of LS1 is tied to the output of DCDC3 while the output of LS1 is connected to the memory-interface supply pin of the SOC. LS1 can be controlled by the internal sequencer, just as any power rail.

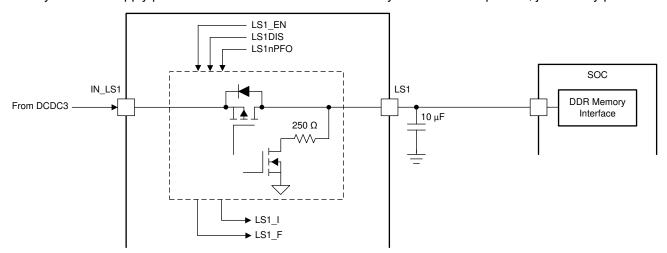


Figure 7-11. Typical Application of Load Switch 1

Product Folder Links: TPS6521845

7.3.1.7.2 Load Switch 2 (LS2)

LS2 is a reverse-blocking, 5 V, low-impedance switch. Load switch 2 provides four different current limit values (100/200/500/1000 mA) that are selectable through LS2ILIM[1:0] bits. Overcurrent is reported through the LS2_I interrupt.

LS2 has its own input-undervoltage protection which forces the switch OFF if the switch input voltage (V_{IN_LS2}) is <2.7 V. Similar to OTS, the LS2_F interrupt is set when the switch is held OFF by the local UVLO function, and the switch recovers automatically when the input voltage rises above the UVLO threshold.

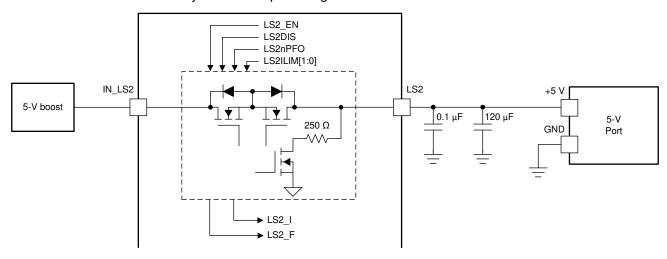


Figure 7-12. Typical Application of Load Switch 2

7.3.1.7.3 Load Switch 3 (LS3)

LS3 is a non-reverse blocking, medium-voltage (< 10 V), low-impedance switch that can be used to provide 1.8-V to 10-V power to an auxiliary port. LS3 has four selectable current limit values that are selectable through LS3ILIM[1:0].

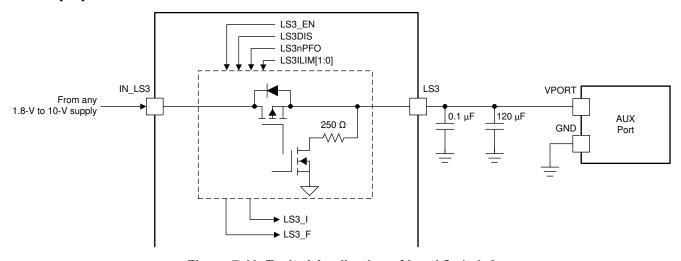


Figure 7-13. Typical Application of Load Switch 3

7.3.1.8 LDO1

LDO1 is a general-purpose LDO intended to provide power to analog circuitry on the SOC. LDO1 has an input voltage range from 1.8 V to 5.5 V, and can be connected either directly to the system power or the output of a DCDC converter. The output voltage is programmable in the range of 0.9 V to 3.4 V with a default of 1.8 V. LDO1 supports up to 200 mA at the minimum specified headroom voltage, and up to 400 mA at the typical operating condition of $V_{OUT} = 1.8 \text{ V}$, V_{IN} LDO1 > 2.7 V.

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7.3.1.9 Coin Cell Battery Voltage Acquisition

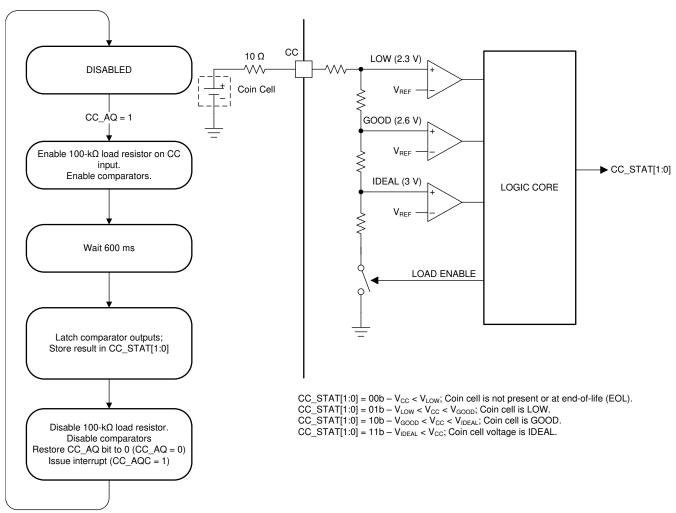


Figure 7-14. Left: Flow Chart for Acquiring Coin Cell Battery Voltage Right: Comparator Circuit

7.3.1.10 UVLO

Depending on the slew rate of the input voltage into the IN_BIAS pin, the power rails of TPS6521845 will be enabled at either V_{ULVO} or $V_{ULVO} + V_{HYS}$.

If the slew rate of the IN_BIAS voltage is greater than 30 V/s, then TPS6521845 will power up at V_{ULVO} . Once the input voltage rises above this level, the input voltage may drop to the V_{UVLO} level before the PMIC shuts down. In this scenario, if the input voltage were to fall below V_{UVLO} but above 2.55 V, the input voltage would have to recover above V_{UVLO} in less than 5 ms for the device to remain active.

If the slew rate of the IN_BIAS voltage is less than 30 V/s, then TPS6521845 will power up at $V_{ULVO} + V_{HYS}$. Once the input voltage rises above this level, the input voltage may drop to the V_{UVLO} level before the PMIC shuts down. In this scenario, if the input voltage were to fall below V_{UVLO} but above 2.5 V, the input voltage would have to recover above $V_{UVLO} + V_{HYS}$ in less than 5 ms for the device to remain active.

In either slew rate scenario, if the input voltage were to fall below 2.5 V, the digital core is reset and all remaining power rails are shut down instantaneously and are pulled low to ground by their internal discharge circuitry (DCDC1-4 and LDO1).

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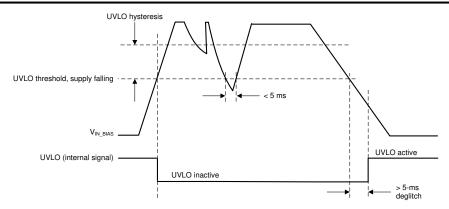


Figure 7-15. Definition of UVLO and Hysteresis, IN_BIAS Slew Rate > 30 V/s

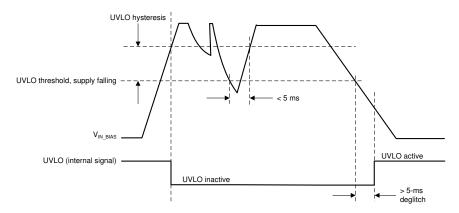


Figure 7-16. Definition of UVLO and Hysteresis, IN_BIAS Slew Rate < 30 V/s

After the UVLO triggers, the internal LDO blocks current flow from its output capacitor back to the IN_BIAS pin, allowing the digital core and the discharge circuits to remain powered for a limited amount of time to properly shut-down and discharge the output rails. The hold-up time is determined by the value of the capacitor connected to INT_LDO. See Section 7.3.1.6 for more details.

7.3.1.11 Power-Fail Comparator

The power-fail comparator notifies the system host if the system supply voltage drops and the system is at risk of shutting down. The comparator has an internal 800-mV threshold and the trip-point is adjusted by an external resistor divider.

By default, the power-fail comparator has no impact on any of the power rails or load switches. Load switches are configured individually, to be disabled when the PFI comparator trips to shed system load and extend hold-up time as described in Section 7.3.1.7. The power-fail comparator also triggers the power-down sequencer, such that all or selective rails power-down when the system voltage fails. To tie the power-fail comparator into the power-down sequence, the OFFnPFO bit in the CONTROL register must be set to 1.

The power-fail comparator cannot be monitored by software, such that no interrupt or status bit is associated to this function.



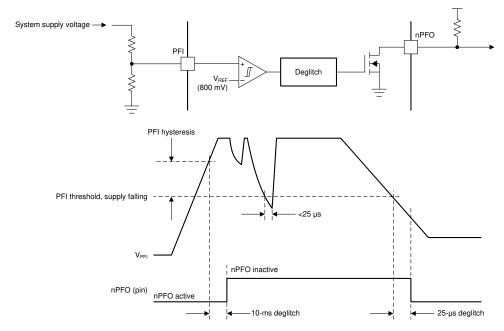


Figure 7-17. Power-Fail Comparator Simplified Circuit and Timing Diagram

7.3.1.12 Battery-Backup Supply Power-Path

DCDC5 and DCDC6 are supplied from either the CC (coin-cell battery) input or IN_BU (main system supply). The power-path is designed to prioritize IN_BU to maximize coin-cell battery life. Whenever the PMIC is powered-up (WAIT_PWR_EN, ACTIVE, SUSPEND, and RECOVERY state), the power-path is forced to select the IN_BU input. In OFF mode the power-path selects the higher of the two inputs with a built-in hysteresis of 150 mV as shown in Figure 7-18.

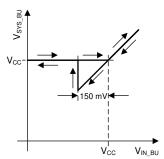
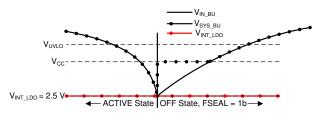
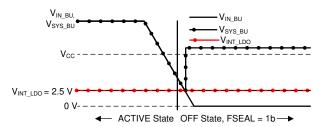


Figure 7-18. Switching Behavior of the Battery-Backup-Supply Power-Path; Power-Path Hysteresis



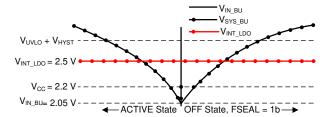
- A. System is supplied by Li-lon battery with a fresh coin-cell backup battery.
- B. (VIN_BIAS slow decay)

Figure 7-20. Switching Behavior of the Battery-Backup-Supply Power-Path; Weakening Main Battery, Strong Coin-Cell



- A. Main Supply is disconnected or decays rapidly.
- B. Rapid decay of VIN BIAS (preregulator)

Figure 7-19. Switching Behavior of the Battery-Backup-Supply Power-Path; Main Power Supply Removal



- System is supplied by Li-lon battery with a weak coin-cell backup battery.
- B. VIN_BIAS slow decay

Figure 7-21. Switching Behavior of the Battery-Backup-Supply Power-Path; Weakening Main Battery, Weak Coin-Cell

When V_{IN_BIAS} drops below the UVLO threshold, the PMIC shuts down all rails and enters OFF mode. At this point the power-path selects the higher of the two input supplies. If the coin-cell battery is less than 150 mV above the UVLO threshold, SYS_BU remains connected to IN_BU (see Figure 7-20). If the coin-cell is >150 mV above the UVLO threshold, the power-path switches to the CC input as shown in Figure 7-21. With no load on the main supply, the input voltage may recover over time to a value greater than the coin-cell voltage and the power-path switches back to IN_BU. This is a typical behavior in a Li-Ion battery powered system.

Depending on the system load, V_{IN_BIAS} may drop below V_{INT_LDO} before the power-down sequence is completed. In that case, INT_LDO is turned OFF and the digital core is reset forcing the unit into OFF mode and the power-path switches to IN_BU as shown in Figure 7-19.

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7.3.1.13 DCDC3 and DCDC4 Power-Up Default Selection

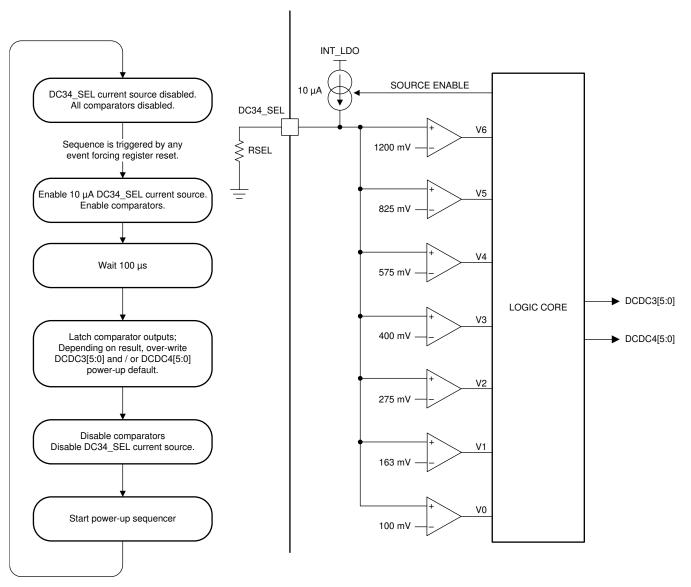


Figure 7-22. Left: Flow Chart for Selecting DCDC Power-Up Default Voltage Right: Comparator Circuit

Table 7-1. Power-Up Default Values of DCDC3 and DCDC4

R	SEL [KΩ]		POWER-UP DEFAULT			
MIN	TYP	MAX	DCDC3[5:0]	DCDC4[5:0]		
0	0	7.7	0xCh (1.2 V)	0x32h (3.3 V)		
11.3	12.1	13	0x12 (1.35 V)	0x32h (3.3 V)		
18.1	20	22	0x18 (1.5 V)	0x32h (3.3 V)		
30.9	31.6	32.3	0x1F (1.8 V)	0x32h (3.3 V)		
44.8	45.3	46.4	0x3D (3.3 V)	0x01 (1.2 V)		
64.2	64.9		0xCh (1.2 V))	0x07 (1.35 V)		
92.9	95.3	96.9	0xCh (1.2 V)	0x0D (1.5 V)		
135.3	150	Tied to INT_LDO	0vCh (1.2 V)	0x14 (1.8 V)		

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7.3.1.14 I/O Configuration

The device has two GPIOs and one GPO pin, which are configured as follows:

- GPIO1:
 - General-purpose, open-drain output is controlled by the GPO1 user bit or sequencer.
 - DDR3 reset input signal from SOC. The signal is either latched or passed-through to the GPO2 pin. See Table 7-2 for details.
- GPO2:
 - General-purpose output is controlled by the GPO2 user bit.
 - DDR3 reset output signal. Signal is controlled by GPIO1 and PGOOD. See Table 7-3 for details.
 - Output buffer is configured as open-drain or push-pull.
- GPIO3:
 - General-purpose, open-drain output id controlled by the GPO3 user bit or sequencer.
 - Reset input-signal for DCDC1 and DCDC2.

Table 7-2. GPIO1 Configuration

IO1_SEL (EEPROM)	GPO1 (USER BIT)	PGOOD (PMIC SIGNAL)	GPIO1 (I/O PIN)	COMMENTS
0	0	X	0	Open-drain output, driving low
0	1	X	HiZ	Open-drain output, HiZ
1	X	0	х	Pin is configured as input and intended as DDR RESET signal. Coming out of POR, GPO2 is driven low. Otherwise, GPO2 status is latched at falling edge of PGOOD. See Figure 7-25.
1	Х	1	0	Pin is configured as input and intended as DDR RESET signal. GPO2 is driven low.
1	Х	1	1	Pin is configured as input and intended as DDR RESET signal. GPO2 is driven high.

Table 7-3. GPO2 Configuration

IO1_SEL (EEPROM)	GPO2_BUF (EEPROM)	GPO2 (USER BIT)	COMMENTS
0	0	0	GPO2 is open drain output controlled by GPO2 user bit (driving low).
0	0	1	GPO2 is open drain output controlled by GPO2 user bit (HiZ).
0	1	0	GPO2 is push-pull output controlled by GPO2 user bit (driving low).
0	1	1	GPO2 is push-pull output controlled by GPO2 user bit (driving high).
1	0	Х	GPO2 is open drain output controlled by GPIO1 and PGOOD.
1	1	Х	GPO2 is push-pull output controlled by GPIO1 and PGOOD.

Table 7-4. GPIO3 Configuration

DC12_RST (EEPROM)	GPO3 (USER BIT)	GPIO3 (I/O PIN)	COMMENTS
0	0	0	Open-drain output, driving low
0	1	HiZ	Open-drain output, HiZ
1	Х	Active low	GPIO3 is DCDC1 and DCDC2 reset input signal to PMIC (active low). See Section 7.3.1.14.2 for details.

7.3.1.14.1 Configuring GPO2 as Open-Drain Output

GPO2 may be configured as open-drain or push-pull output. The supply for the push-pull driver is internally connected to the IN_LS1 input pin, whereas an external pull-up resistor and supply are required in the open-drain configuration. Because of the internal connection to IN_LS1, the external pull-up supply must not exceed the voltage on the IN_LS1 pin, otherwise leakage current may be observed from GPO2 to IN_LS1 as shown in Figure 7-23.

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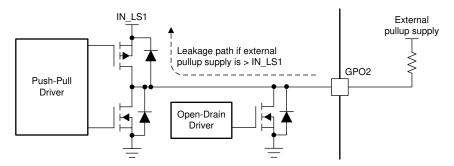


Figure 7-23. GPO2 as Open-Drain Output

Note

When configured as open-drain output, the external pull-up supply must not exceed the voltage level on IN_LS1 pin.

7.3.1.14.2 Using GPIO3 as Reset Signal to DCDC1 and DCDC2

The GPIO3 is an edge-sensitive reset input to the PMIC, when the DC12_RST bit set to 1. The reset signal affects DCDC1 and DCDC2 only, so that only those two registers are reset to the power-up default whenever GPIO3 input transitions from high to low, while all other registers maintain their current values. DCDC1 and DCDC2 transition back to the default value following the SLEW settings, and are not power cycled. This function recovers the processor from reset events while in low-power mode.

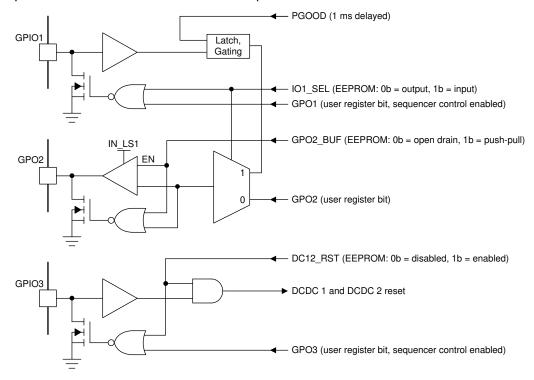


Figure 7-24. I/O Pin Logic

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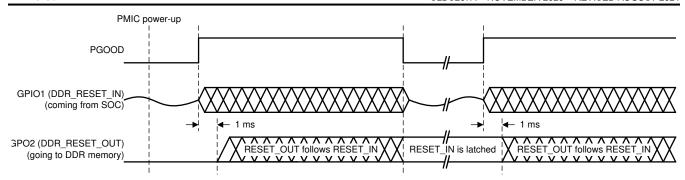


Figure 7-25. DDR3 Reset Timing Diagram

Note

GPIO must be configured as input (IO1 SEL = 1b). GPO2 is automatically configured as output.

7.3.1.15 Push Button Input (PB)

The PB pin is a CMOS-type input used to power-up the PMIC. Typically, the PB pin is connected to a momentary switch to ground and an external pullup resistor. The power-up sequence is triggered if the PB input is held low for 600 ms.

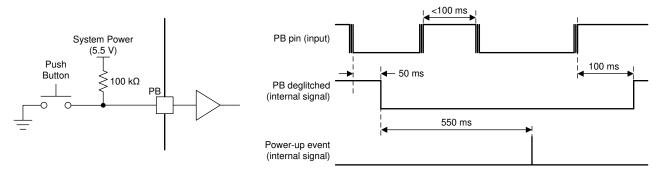


Figure 7-26. Left: Typical PB Input Circuit Right: Push-Button Input (PB) Deglitch and Power-Up Timing

In ACTIVE mode, the TPS6521845 monitors the PB input and issues an interrupt when the pin status changes, such as when it drops below or rises above the PB input-low or input-high thresholds. The interrupt is masked by the PBM bit in the INT_MASK1 register.



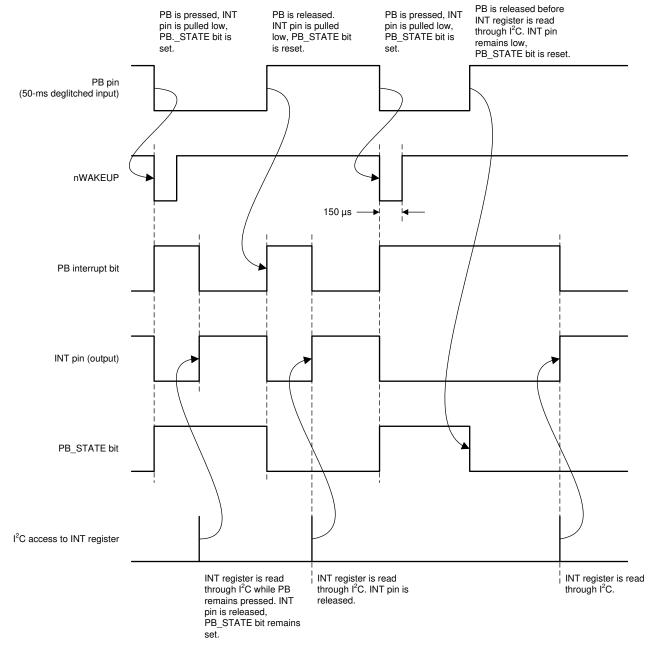


Figure 7-27. PB Input-Low or Input-High Thresholds

Note

Interrupts are issued whenever the PB pin status changes. The PB_STATE bit reflects the current status of the PB input. nWAKEUP is pulled low for 150 μ s on every falling edge of PB.

7.3.1.15.1 Signaling PB-Low Event on the nWAKEUP Pin

In ACTIVE state, the nWAKEUP pin is pulled low for five 32-kHz clock cycles (approximately 150 μ s) whenever a falling edge on the PB input is detected. This allows the host processor to wakeup from DEEP SLEEP mode of operation. It is recommended to pull-up the nWAKEUP pin to DCDC6 output through a 1-M Ω resistor .

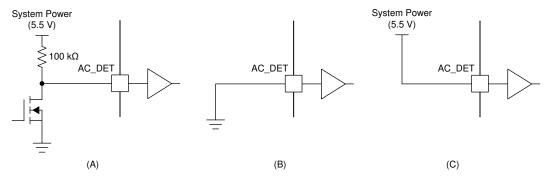
7.3.1.15.2 Push Button Reset

If the PB input is pulled low for 8 s (15 s if TRST = 1b) or longer, then all rails except for DCDC5 and DCDC6 are disabled, and the device enters the RECOVERY state. The device powers up automatically after the 500 ms power-down sequence is complete, regardless of the state of the PB input. Holding the PB pin low for 8 s (15 s if TRST = 1b), only turns off the device temporarily and forces a system restart, and is not a power-down function. If the PB is held low continuously, the device power-cycles in 8-s and 15-s intervals.

7.3.1.16 AC_DET Input (AC_DET)

The AC DET pin is a CMOS-type input used in three different ways to control the power-up of the PMIC:

- In a battery operated system, AC_DET is typically connected to an external battery charger with an opendrain power-good output pulled low when a valid charger supply is connected to the system. A falling edge on the AC_DET pin causes the PMIC to power up.
- In a non-portable system, the AC_DET pin may be shorted to ground and the device powers up whenever system power is applied to the chip.
- If none of the above behaviors are desired, AC_DET may be tied to system power (IN_BIAS). Power-up is then controlled through the push-button input or PWR_EN input.



- A. Portable Systems
- B. Non-portable Systems
- C. Disabled

Figure 7-28. AC_DET Pin Configurations

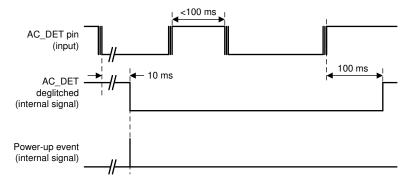


Figure 7-29. AC_DET Input Deglitch and Power-Up Timing (Portable Systems)

In ACTIVE state, the TPS6521845 monitors the AC_DET input and issues an interrupt when the pin status changes, such as when it drops below or rises above the AC_DET input-low or input-high thresholds. The interrupt is masked by the ACM bit in the INT_MASK1 register.

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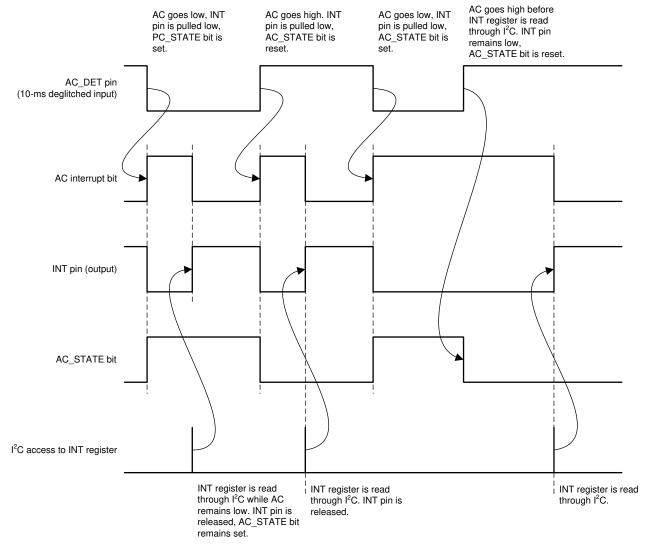


Figure 7-30. AC_STATE Pin

Note

Interrupts are issued whenever the AC_DET pin status changes. The AC_STATE bit reflects the current status of the AC_DET input.

7.3.1.17 Interrupt Pin (INT)

The interrupt pin signals any event or fault condition to the host processor. Whenever a fault or event occurs in the device, the corresponding interrupt bit is set in the INT register, and the open-drain output is pulled low. The INT pin is released (returns to Hi-Z state) and fault bits are cleared when the host reads the INT register. If a failure persists, the corresponding INT bit remains set and the INT pin is pulled low again after a maximum of 32 µs.

The MASK register masks events from generating interrupts. The MASK settings affect the INT pin only, and have no impact on the protection and monitor circuits.

7.3.1.18 I²C Bus Operation

The TPS6521845 hosts a slave I²C interface (address 0x24) that supports data rates up to 400 kbps, auto-increment addressing. ¹

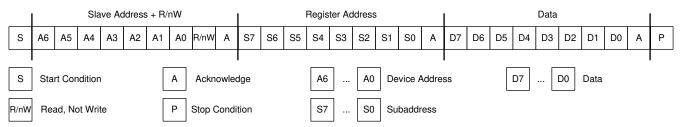


Figure 7-31. Subaddress in I²C Transmission

The I²C bus is a communications link between a controller and a series of slave terminals. The link is established using a two-wired bus consisting of a serial clock signal (SCL) and a serial data signal (SDA). The serial clock is sourced from the controller in all cases where the serial data line is bi-directional for data communication between the controller and the slave terminals. Each device has an open drain output to transmit data on the serial data line. An external pullup resistor must be placed on the serial data line to pull the drain output high during data transmission.

Data transmission initiates with a start bit from the controller as shown in Figure 7-33. The start condition is recognized when the SDA line transitions from high to low during the high portion of the SCL signal. Upon reception of a start bit, the device receives serial data on the SDA input and checks for valid address and control information. If the appropriate slave address is set for the device, the device issues an acknowledge pulse and prepares to receive register address and data. Data transmission is completed by either the reception of a stop condition or the reception of the data word sent to the device. A stop condition is recognized as a low to high transition of the SDA input during the high portion of the SCL signal. All other transitions of the SDA line must occur during the low portion of the SCL signal. An acknowledge issues after the reception of valid slave address, register-address, and data words. The I²C interfaces an auto-sequence through the register addresses, so that multiple data words can be sent for a given I²C transmission. Reference Figure 7-32 and Figure 7-33 for details.

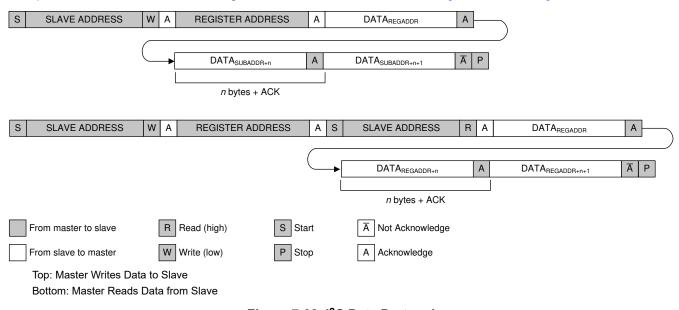


Figure 7-32. I²C Data Protocol

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¹ Note: The SCL duty cycle at 400 kHz must be >40%.



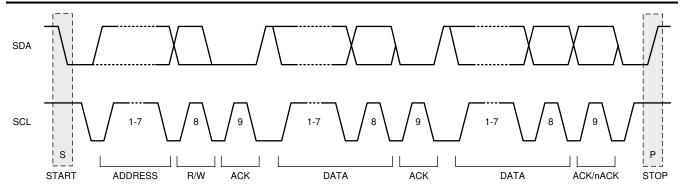


Figure 7-33. I²C Protocol and Transmission Timing I²C Start Stop and Acknowledge Protocol

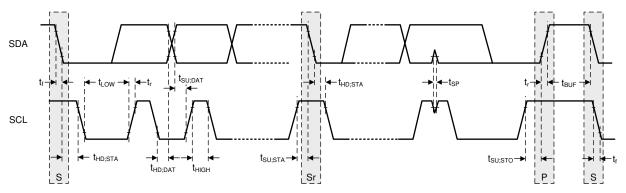
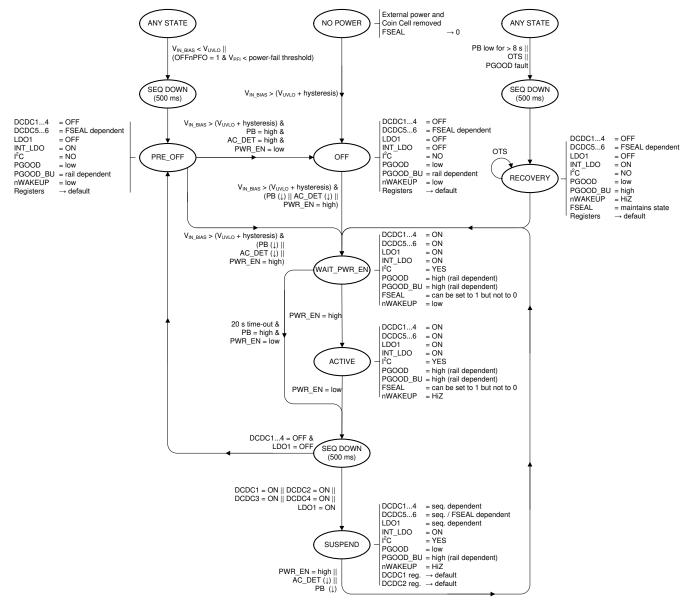


Figure 7-34. I²C Protocol and Transmission Timing I²C Data Transmission Timing

7.4 Device Functional Modes

7.4.1 Modes of Operation



PB (↓) has 50 ms debounce.

AC_DET (↓) has 10 ms debounce.

 (\downarrow) = denotes falling edge of signal.

Figure 7-35. Modes of Operation Diagram

7.4.2 OFF

In OFF mode, the PMIC is completely shut down with the exception of a few circuits to monitor the AC_DET, PWR_EN, and PB input. All power rails are turned off and the registers are reset to their default values. The I^2C communication interface is turned off. This is the lowest-power mode of operation. To exit OFF mode V_{IN_BIAS} must exceed the UVLO threshold and one of the following wake-up events must occur:

- The PB input is pulled low.
- THE AC_DET input is pulled low.
- The PWR_EN input is pulled high.

To enter the OFF state, ensure that all power rails are assigned to the sequencer, then pull the PWR_EN pin low. Additionally, if the OFFnPFO bit is set to 1b and the PFI input falls below the power fail threshold the device transitions to the OFF state. If the freshness seal is broken, DCDC5 and DCDC6 remains on in the OFF state. If a PGOOD or OTS fault occurs while in the ACTIVE state, TPS6521845 will transition to the RESET state.

7.4.3 ACTIVE

This is the typical mode of operation when the system is up and running. All DCDC converters, LDOs, and load switches are operational and can be controlled through the I²C interface. After a wake-up event, the PMIC enables all rails controlled by the sequencer and pulls the nWAKEUP pin low to signal the event to the host processor. The device only enters the ACTIVE state if the host asserts the PWR_EN pin within 20 s after the wake-up event. Otherwise it will enter the OFF state. The nWAKEUP pin returns to HiZ mode after the PWR_EN pin is asserted. The ACTIVE state can also be directly entered from the SUSPEND state by pulling the PWR_EN pin high. See the SUSPEND state description for details. To exit the ACTIVE mode, the PWR_EN pin must be pulled low.

7.4.4 SUSPEND

The SUSPEND state is a low-power mode of operation intended to support system standby. Typically all power rails are turned off with the exception of any rail with an SEQ register set to 0h. DCDC5 and DCDC6 also remain enabled if the freshness seal is broken. To enter the SUSPEND state, pull the PWR_EN pin low. All power rails controlled by the power-down sequencer are shut down, and after 500 ms the device enters the SUSPEND state. All rails not controlled by the power-down sequencer will maintain its state. Note: all register values are reset as the device enters the SUSPEND state. The device enters the ACTIVE state after it detects a wake-up event as described in the previous sections.

7.4.5 RESET

The TPS6521845 can be reset by holding the PB pin low for more than 8 or 15 s, depending on the value of the TRST bit. All rails are shut down by the sequencer and all register values reset to their default values. Rails not controlled by the sequencer are shut down additionally. Note: the RESET function power-cycles the device and only temporarily shuts down the output rails. Resetting the device does not lead to an OFF state. If the PB_IN pin is kept low for an extended amount of time, the device continues to cycle between the ACTIVE and RESET state, entering the RESET every 8 or 15 s.

The device is also reset if a PGOOD or OTS fault occurs. The TPS6521845 remains in the RECOVERY state until the fault is removed, at which time it transitions back to the ACTIVE state.

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7.5 Register Maps

7.5.1 Password Protection

Registers 0x11 through 0x26 are protected against accidental write by a 8-bit password. The password must be written prior to writing to a protected register and automatically resets to 0x00 after the next I²C transaction, regardless of the register accessed or transaction type (read or write). The password is required for write access only and is not required for read access.

To write to a protected register:

- 1. Write the address of the destination register, XORed with the protection password (0x7D), to the PASSWORD register (0x10).
- 2. Write the data to the password protected register.
- 3. If the content of the PASSWORD register is XORed, with an address send that matches 0x7D, then the data transfers to the protected register. Otherwise, the transaction is ignored. In either case the PASSWORD register resets to 0x00 after the transaction.

The cycle must be repeated for any other register that is Level1 write protected.

7.5.2 Freshness Seal (FSEAL) Bit

The FSEAL (freshness seal) bit prevents accidental shut-down of the always-on supplies, DCDC5 and DCDC6. The FSEAL bit exists in a default state of 0b, and can be set to 1b and reset to 0b once for factory testing. The second time the bit is set to 1b, it remains 1b and cannot reset again under software control. Coin-cell battery and main supply must be disconnected from the device to reset the FSEAL bit again. With the FSEAL bit set to 1b, DCDC5 and DCDC6 are forced ON regardless of the state of the DC5_EN and DC6_EN bit, and the rails do not turn off when the device enters the OFF state.

A consecutive write of [0xB1, 0xFE, and 0xA3] to the password register sets the FSEAL bit to 1b. The three bytes must be written consecutively for the sequence to be valid. No other read or write transactions are allowed between the three bytes, or the sequence is invalid. After a valid sequence, the FSEAL bit in the STATUS register reflects the new setting.

After setting the FSEAL bit, the device can enter the OFF state or any other mode of operation without affecting the state of the FSEAL bit, provided the coin-cell supply remains connected to the chip.

A second write of [0xB1, 0xFE, and 0xA3] to the password register resets the FSEAL bit to 0b. The three bytes must be written consecutively for the sequence to be valid.

A third write of [0xB1, 0xFE, and 0xA3] to the password register sets the FSEAL bit to 1b and locks it into this state for as long as the coin-cell supply (CC) remains connected to the device.

7.5.3 FLAG Register

The FLAG register contains a bit for each power rail and GPO to keep track of the enable state of the rails while the system is suspended. The following rules apply to the FLAG register:

- The power-up default value for any flag bit is 0.
- Flag bits are read-only and cannot be written to.
- Upon entering a SUSPEND state, the flag bits are set to same value as their corresponding ENABLE bits.
 Rails and GPOs enabled in a SUSPEND state have flag bits set to 1, while all other flag bits are set to 0. Flag bits are not updated while in the SUSPEND state or when exiting the SUSPEND state.
- The FLAG register is static in WAIT_PWR_EN and ACTIVE state. The FLAG register reflects the enable state
 of DCDC1, DCDC2, DCDC3, DCDC4, and LDO1; and, reflects the enable state of GPO1, GPO2, and GPO3
 during the last SUSPEND state.

The host processor reads the FLAG register to determine if the system powered up from the OFF or SUSPEND state. In the SUSPEND state, typically the DDR memory is kept in self refresh mode and therefore the DC3_FLG or DC4_FLG bits are set.



7.5.4 TPS6521845 Registers

Table 7-5 lists the memory-mapped registers for the TPS6521845. All register offset addresses not listed in Table 7-5 should be considered as reserved locations and the register contents should not be modified.

Table 7-5. TPS6521845 Registers

SUBADDRESS	ACRONYM	REGISTER NAME	R/W	PASSWORD PROTECTED	SECTION
0x00	CHIPID	CHIP ID	R	No	Section 7.5.5
0x01	INT1	INTERRUPT 1	R	No	Section 7.5.6
0x02	INT2	INTERRUPT 2	R	No	Section 7.5.7
0x03	INT_MASK1	INTERRUPT MASK 1	R/W	No	Section 7.5.8
0x04	INT_MASK2	INTERRUPT MASK 2	R/W	No	Section 7.5.9
0x05	STATUS	STATUS	R	No	Section 7.5.10
0x06	CONTROL	CONTROL	R/W	No	Section 7.5.11
0x07	FLAG	FLAG	R	No	Section 7.5.12
0x10	PASSWORD	PASSWORD	R/W	No	Section 7.5.13
0x11	ENABLE1	ENABLE 1	R/W	Yes	Section 7.5.14
0x12	ENABLE2	ENABLE 2	R/W	Yes	Section 7.5.15
0x13	CONFIG1	CONFIGURATION 1	R/W	Yes	Section 7.5.16
0x14	CONFIG2	CONFIGURATION 2	R/W	Yes	Section 7.5.17
0x15	CONFIG3	CONFIGURATION 3	R/W	Yes	Section 7.5.18
0x16	DCDC1	DCDC1 CONTROL	R/W	Yes	Section 7.5.19
0x17	DCDC2	DCDC2 CONTROL	R/W	Yes	Section 7.5.20
0x18	DCDC3	DCDC3 CONTROL	R/W	Yes	Section 7.5.21
0x19	DCDC4	DCDC4 CONTROL	R/W	Yes	Section 7.5.22
0x1A	SLEW	SLEW RATE CONTROL	R/W	Yes	Section 7.5.23
0x1B	LDO1	LDO1 CONTROL	R/W	Yes	Section 7.5.24
0x20	SEQ1	SEQUENCER 1	R/W	Yes	Section 7.5.25
0x21	SEQ2	SEQUENCER 2	R/W	Yes	Section 7.5.26
0x22	SEQ3	SEQUENCER 3	R/W	Yes	Section 7.5.27
0x23	SEQ4	SEQUENCER 4	R/W	Yes	Section 7.5.28
0x24	SEQ5	SEQUENCER 5	R/W	Yes	Section 7.5.29
0x25	SEQ6	SEQUENCER 6	R/W	Yes	Section 7.5.30
0x26	SEQ7	SEQUENCER 7	R/W	Yes	Section 7.5.31

Table 7-6 explains the common abbreviations used in this section.

Table 7-6. Common Abbreviations

Abbreviation	Description
R	Read
W	Write
R/W	Read and write capable
h	Hexadecimal notation of a group of bits
b	Hexadecimal notation of a bit or group of bits
Х	Do not care reset value

7.5.5 CHIPID Register (subaddress = 0x00) [reset = 0x45]

CHIPID is shown in Figure 7-31 and described in Table 7-7.

Return to Table 7-5.

Figure 7-31. CHIPID Register

7	6	5	4	3	2	1	0
CHIP						REV	
		R-8h				R-5h	

Table 7-7. CHIPID Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-3	CHIP	R	8h	Chip ID: 0h = TPS65218 1h = Future use 2h = TPS6521815 3h = Future use 4h = TPS6521825 5h = Future use 6h = TPS6521835 7h = Future use 8h = TPS6521845 9h = Future use Ah = TPS6521855 1Fh = Future use
2-0	REV	R	5h	Revision code: 0h = Revision 1.0 1h = Revision 1.1 2h = Revision 2.0 3h = Revision 2.1 4h = Revision 3.0 5h = Revision 4.0 (D0) 6h = Future use 7h = Future use

7.5.6 INT1 Register (subaddress = 0x01) [reset = 0x00]

INT1 is shown in Figure 7-32 and described in Table 7-8.

Return to Table 7-5.

Figure 7-32. INT1 Register

7	6	5	4	3	2	1	0
RESE	RVED	VPRG	AC	РВ	НОТ	CC_AQC	PRGC
R-0	0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

Table 7-8. INT1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	
5	VPRG	R	0b	Programming voltage interrupt: 0b = No significance. 1b = Input voltage is too low for programming power-up default values.



Table 7-8. INT1 Register Field Descriptions (continued)

Table 1-6. INTT Register Field Descriptions (Continued)								
Bit	Field	Туре	Reset	Description				
4	AC	R	Ob	AC_DET pin status change interrupt. Note: Status information is available in STATUS register. 0b = No change in status. 1b = AC_DET status change (AC_DET pin changed high to low or low to high).				
3	РВ	R	Ob	Push-button status change interrupt. Note: Status information is available in STATUS register 0b = No change in status. 1b = Push-button status change (PB changed high to low or low to high).				
2	нот	R	0b	Thermal shutdown early warning: 0b = Chip temperature is below HOT threshold. 1b = Chip temperature exceeds HOT threshold.				
1	CC_AQC	R	0b	Coin cell battery voltage acquisition complete interrupt: 0b = No significance. 1b = Backup battery status comparators have settled and results are available in STATUS register.				
0	PRGC	R	0b	EEPROM programming complete interrupt: 0b = No significance. 1b = Programming of power-up default settings has completed successfully.				

7.5.7 INT2 Register (subaddress = 0x02) [reset = 0x00]

INT2 is shown in Figure 7-33 and described in Table 7-9.

Return to Table 7-5.

Figure 7-33. INT2 Register

7	6	5	4	3	2	1	0
RESE	RVED	LS3_F	LS2_F	LS1_F	LS3_I	LS2_I	LS1_I
R-0	00b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

Table 7-9. INT2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	
5	LS3_F	R	0b	Load switch 3 fault interrupt: 0b = No fault. Switch is working normally. 1b = Load switch exceeded operating temperature limit and is temporarily disabled.
4	LS2_F	R	Ob	Load switch 2 fault interrupt: 0b = No fault. Switch is working normally. 1b = Load switch exceeded operating temperature limit or input voltage dropped below minimum value. Switch is temporarily disabled.
3	LS1_F	R	0b	Load switch 1 fault interrupt: 0b = No fault. Switch is working normally. 1b = Load switch exceeded operating temperature limit and is temporarily disabled.

Table 7-9. INT2 Register Field Descriptions (continued)

	Table 7-3. IN 12 Register Field Descriptions (Continued)									
Bit	Field	Туре	Reset	Description						
2	LS3_I	R	0b	Load switch 3 current-limit interrupt: 0b = Load switch is disabled or not in current limit. 1b = Load switch is actively limiting the output current (output load is exceeding current limit value).						
1	LS2_I	R	0b	Load switch 2 current-limit interrupt: 0b = Load switch is disabled or not in current limit. 1b = Load switch is actively limiting the output current (output load is exceeding current limit value).						
0	LS1_I	R	0b	Load switch 1 current-limit interrupt: 0b = Load switch is disabled or not in current limit. 1b = Load switch is actively limiting the output current (output load is exceeding current limit value).						

7.5.8 INT_MASK1 Register (subaddress = 0x03) [reset = 0x00]

 $\ensuremath{\mathsf{INT_MASK1}}$ is shown in Figure 7-34 and described in Table 7-10.

Return to Table 7-5.

Figure 7-34. INT_MASK1 Register

_								
	7	6	5	4	3	2	1	0
	RESE	RVED	VPRGM	ACM	РВМ	НОТМ	CC_AQCM	PRGCM
	R-0	00b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b

Table 7-10. INT_MASK1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	
5	VPRGM	R/W	0b	Programming voltage interrupt mask bit. Note: mask bit has no effect on monitoring function: 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
4	ACM	R/W	0b	AC_DET interrupt masking bit: 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin). Note: mask bit has no effect on monitoring function.
3	РВМ	R/W	0b	PB interrupt masking bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
2	НОТМ	R/W	0b	HOT interrupt masking bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
1	CC_AQCM	R/W	0b	C_AQC interrupt masking bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).

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Table 7-10. INT_MASK1 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description		
0	PRGCM	R/W	0b	PRGC interrupt masking bit. Note: mask bit has no effect on		
				monitoring function.		
				0b = Interrupt is unmasked (interrupt event pulls nINT pin low).		
				1b = Interrupt is masked (interrupt has no effect on nINT pin).		

7.5.9 INT_MASK2 Register (subaddress = 0x04) [reset = 0x00]

INT_MASK2 is shown in Figure 7-35 and described in Table 7-11.

Return to Table 7-5.

Figure 7-35. INT_MASK2 Register

7 6	5	4	3	2	1	0
RESERVED	LS3_FM	LS2_FM	LS1_FM	LS3_IM	LS2_IM	LS1_IM
R-00b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b

Table 7-11. INT_MASK2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	
5	LS3_FM	R/W	0b	LS3 fault interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
4	LS2_FM	R/W	Ob	LS2 fault interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
3	LS1_FM	R/W	Ob	LS1 fault interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
2	LS3_IM	R/W	Ob	LS3 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
1	LS2_IM	R/W	Ob	LS2 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).
0	LS1_IM	R/W	ОЬ	LS1 current-limit interrupt mask bit. Note: mask bit has no effect on monitoring function. 0b = Interrupt is unmasked (interrupt event pulls nINT pin low). 1b = Interrupt is masked (interrupt has no effect on nINT pin).

7.5.10 STATUS Register (subaddress = 0x05) [reset = 00XXXXXXb]

Register mask: C0h

STATUS is shown in Figure 7-36 and is described in Table 7-12.

Return to Table 7-5.

Figure 7-36. STATUS Register

7	6	5	4	3	2	1	0
FSEAL	EE	AC_STATE	PB_STATE	STA	ATE	CC_S	STAT
R-0b	R-0b	R-X	R-X	R	-X	R-2	X

Table 7-12. STATUS Register Field Descriptions

Bit	Field	Type	Reset	Description		
				Description		
7	FSEAL	R	0b	Freshness seal (FSEAL) status. Note: See Section 7.5.2 for details. 0b = FSEAL is in native state (fresh). 1b = FSEAL is broken.		
6	EE	R	0b	EEPROM status: 0b = EEPROM values have not been changed from factory default setting. 1b = EEPROM values have been changed from factory default settings.		
5	AC_STATE	R	Х	AC_DET input status bit: 0b = AC_DET input is inactive (AC_DET input pin is high). 1b = AC_DET input is active (AC_DET input is low).		
4	PB_STATE	R	X	PB input status bit: 0b = Push Button input is inactive (PB input pin is high). 1b = Push Button input is active (PB input pin is low).		
3-2	STATE	R	X	State machine STATE indication: 0h = PMIC is in transitional state. 1h = PMIC is in WAIT_PWR_EN state. 2h = PMIC is in ACTIVE state. 3h = PMIC is in SUSPEND state.		
1-0	CC_STAT	R	X	Coin cell state of charge. Note: Coin-cell voltage acquisition must be triggered first before status bits are valid. See CC_AQ bit in Section 7.5.11. Oh = V _{CC} < V _{LOW_LEVEL} ; Coin cell is not present or approaching end-of-life (EOL). 1h = V _{LOW_LEVEL} < V _{CC} < V _{GOOD_LEVEL} ; Coin cell voltage is LOW. 2h = V _{GOOD_LEVEL} < V _{CC} < V _{IDEAL_LEVEL} ; Coin cell voltage is GOOD. 3h = V _{IDEAL} < V _{CC} ; Coin cell voltage is IDEAL.		

7.5.11 CONTROL Register (subaddress = 0x06) [reset = 0x00]

CONTROL is shown in Figure 7-37 and described in Table 7-13.

Return to Table 7-5.

Figure 7-37. CONTROL Register

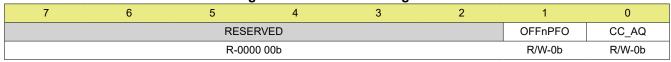


Table 7-13. CONTROL Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-2	RESERVED	R	0000 00b	

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Table 7-13. CONTROL Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
1	OFFnPFO	R/W	0b	Power-fail shutdown bit: 0b = nPFO has no effect on PMIC state. 1b = All rails are shut down and PMIC enters OFF state when PFI comparator trips (nPFO is low).
0	CC_AQ	R/W	0b	Coin Cell battery voltage acquisition start bit: 0b = No significance 1b = Triggers voltage acquisition. Bit is automatically reset to 0.

7.5.12 FLAG Register (subaddress = 0x07) [reset = 0x00]

FLAG is shown in Figure 7-38 and described in Table 7-14.

Return to Table 7-5.

Figure 7-38. FLAG Register

7	6	5	4	3	2	1	0
GPO3_FLG	GPO2_FLG	GPO1_FLG	LDO1_FLG	DC4_FLG	DC3_FLG	DC2_FLG	DC1_FLG
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

Table 7-14. FLAG Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	GPO3_FLG	R	0b	GPO3 Flag bit: 0b = Device powered up from OFF or SUSPEND state and GPO3 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and GPO3 was enabled while in SUSPEND.
6	GPO2_FLG	R	Ob	GPO2 Flag bit 0b = Device powered up from OFF or SUSPEND state and GPO2 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and GPO2 was enabled while in SUSPEND.
5	GPO1_FLG	R	0b	GPO1 Flag bit: 0b = Device powered up from OFF or SUSPEND state and GPO1 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and GPO1 was enabled while in SUSPEND.
4	LDO1_FLG	R	0b	LDO1 Flag bit: 0b = Device powered up from OFF or SUSPEND state and LDO1 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and LDO1 was enabled while in SUSPEND.
3	DC4_FLG	R	0b	DCDC4 Flag bit: 0b = Device powered up from OFF or SUSPEND state and DCDC4 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and DCDC4 was enabled while in SUSPEND.

Table 7-14. FLAG Register Field Descriptions (continued)

	Table 7-14. FLAG Register Field Descriptions (continued)									
Bit	Field	Туре	Reset	Description						
2	DC3_FLG	R	Ob	DCDC3 Flag bit: 0b = Device powered up from OFF or SUSPEND state and DCDC3 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and DCDC3 was enabled while in SUSPEND.						
1	DC2_FLG	R	0b	DCDC2 Flag bit: 0b = Device powered up from OFF or SUSPEND state and DCDC2 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and DCDC2 was enabled while in SUSPEND.						
0	DC1_FLG	R	0b	DCDC1 Flag bit: 0b = Device powered up from OFF or SUSPEND state and DCDC1 was disabled while in SUSPEND. 1b = Device powered up from SUSPEND state and GDCDC1PO3 was enabled while in SUSPEND.						

7.5.13 PASSWORD Register (subaddress = 0x10) [reset = 0x00]

PASSWORD is shown in Figure 7-39 and described in Table 7-15.

Return to Table 7-5.

Figure 7-39. PASSWORD Register

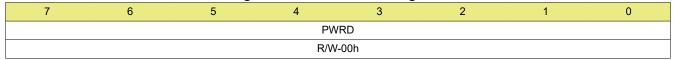


Table 7-15. PASSWORD Register Field Descriptions

Bit	Field	Туре	Reset	Description		
7-0	PWRD	R/W		Register is used for accessing password protected registers (see Section 7.5.1 for details). Breaking the freshness seal (see Section 7.5.2 for details). Programming power-up default values . Read-back always yields 0x00.		



7.5.14 ENABLE1 Register (subaddress = 0x11) [reset = 0x00]

ENABLE1 is shown in Figure 7-40 and described in Table 7-16.

Return to Table 7-5.

Password protected.

Figure 7-40. ENABLE1 Register

7	6	5	4	3	2	1	0
RESE	RVED	DC6_EN	DC5_EN	DC4_EN	DC3_EN	DC2_EN	DC1_EN
R-0	0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b	R/W-0b

Table 7-16. ENABLE1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	200111111111
5	DC6_EN	R/W	Ob	DCDC6 enable bit. DCDC6 can only be disabled if FSEAL = 0. See Section 7.5.2 for details. 0b = Disabled 1b = Enabled
4	DC5_EN	R/W	0b	DCDC5 enable bit. Note: At power-up and down this bit is automatically updated by the internal power sequencer. DCDC5 can only be disabled if FSEAL = 0. See Section 7.5.2 for details. 0b = Disabled 1b = Enabled
3	DC4_EN	R/W	Ob	DCDC4 enable bit. Note: At power-up and down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled
2	DC3_EN	R/W	Ob	DCDC3 enable bit. Note: At power-up and down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled
1	DC2_EN	R/W	0b	DCDC2 enable bit. Note: At power-up and down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled
0	DC1_EN	R/W	0b	DCDC1 enable bit. Note: At power-up and down this bit is automatically updated by the internal power sequencer. 0b = Disabled 1b = Enabled

7.5.15 ENABLE2 Register (subaddress = 0x12) [reset = 0x00]

ENABLE2 is shown in Figure 7-41 and described in Table 7-17.

Return to Table 7-5.

Password protected.

Figure 7-41. ENABLE2 Register

	7	6	5	4	3	2	1	0
RES	SERVED	GPIO3	GPIO2	GPIO1	LS3_EN	LS2_EN	LS1_EN	LDO1_EN
	R-0b	R/W-0b						

Table 7-17. ENABLE2 Register Field Descriptions

Bit	Field	Туре	Reset	Register Field Descriptions Description
7	RESERVED	R	0b	
6	GPIO3	R/W	0b	General purpose output 3 / reset polarity. Note: If DC12_RST bit (register 0x14) is set to 1 this bit has no function. 0b = GPIO3 output is driven low. 1b = GPIO3 output is HiZ.
5	GPIO2	R/W	0b	General purpose output 2. Note: If IO_SEL bit (register 0x13) is set to 1 this bit has no function. 0b = GPO2 output is driven low. 1b = GPO2 output is HiZ.
4	GPIO1	R/W	0b	General purpose output 1. Note: If IO_SEL bit (register 0x13) is set to 1 this bit has no function. 0b = GPO1 output is driven low. 1b = GPO1 output is HiZ.
3	LS3_EN	R/W	0b	Load switch 3 (LS3) enable bit. 0b = Disabled 1b = Enabled
2	LS2_EN	R/W	0b	Load switch 2 (LS2) enable bit. 0b = Disabled 1b = Enabled
1	LS1_EN	R/W	Ob	Load switch 1 (LS1) enable bit. 0b = Disabled 1b = Enabled Note: At power-up and down this bit is automatically updated by the internal power sequencer.
0	LDO1_EN	R/W	Ob	LDO1 enable bit. 0b = Disabled 1b = Enabled Note: At power-up and down this bit is automatically updated by the internal power sequencer.

7.5.16 CONFIG1 Register (subaddress = 0x13) [reset = 0x08]

CONFIG1 is shown in Figure 7-42 and described in Table 7-18.

Return to Table 7-5.

Password protected.

Figure 7-42. CONFIG1 Register

7	6	5	4	3	2	1	0
TRST	GPO2_BUF	IO1_SEL	PGDL	Y	STRICT	UV	LO
R/W-0b	R/W-0b	R/W-0b	R/W-0	1b	R/W-0b	R/W-	-00b

Table 7-18. CONFIG1 Register Field Descriptions

				<u> </u>
Bit	Field	Туре	Reset	Description
7	TRST	R/W	0b	Push-button reset time constant:
				0b = 8 s
				1b = 15 s

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Table 7-18. CONFIG1 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description (continued)
6	GPO2_BUF	R/W	0b	GPO2 output buffer configuration: 0b = GPO2 buffer is configured as open-drain. 1b = GPO2 buffer is configured as push-pull (high-level is driven to IN_LS1).
5	IO1_SEL	R/W	Ob	GPIO1 / GPO2 configuration bit. See Section 7.3.1.14 for details. 0b = GPIO1 is configured as general-purpose, open-drain output. GPO2 is independent output. 1b = GPIO1 is configured as input, controlling GPO2. Intended for DDR3 reset signal control.
4-3	PGDLY	R/W	01b	Power-Good delay. Note: Power-good delay applies to rising-edge only (power-up), not falling edge (power-down or fault). 00b = 10 ms 01b = 20 ms 10b = 50 ms 11b = 150 ms
2	STRICT	R/W	0b	Supply Voltage Supervisor Sensitivity selection. See Section 6.5 for details. 0b = Power-good threshold (VOUT falling) has wider limits. Overvoltage is not monitored. 1b = Power-good threshold (VOUT falling) has tight limits. Overvoltage is monitored.
1-0	UVLO	R/W	00Ь	UVLO setting 00b = 2.75 V 01b = 2.95 V 10b = 3.25 V 11b = 3.35 V

7.5.17 CONFIG2 Register (subaddress = 0x14) [reset = 0x40]

CONFIG2 is shown in Figure 7-43 and described in Table 7-19.

Return to Table 7-5.

Password protected.

Figure 7-43. CONFIG2 Register

7	6	5	4	3	2	1	0
DC12_RST	UVLOHYS	RESERVED		LS3ILIM		LS2ILIM	
R/W-0b	R/W-1b	R-00b		R/W	-00b	R/W-	-00b

Table 7-19. CONFIG2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	DC12_RST	R/W		DCDC1 and DCDC2 reset-pin enable: 0b = GPIO3 is configured as general-purpose output. 1b = GPIO3 is configured as warm-reset input to DCDC1 and DCDC2.
6	UVLOHYS	R/W		UVLO hysteresis: 0b = 200 mV 1b = 400 mV
5-4	RESERVED	R	00b	

Table 7-19. CONFIG2 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
3-2	LS3ILIM	R/W	00b	Load switch 3 (LS3) current limit selection:
				00b = 100 mA, (MIN = 98 mA)
				01b = 200 mA, (MIN = 194 mA)
				10b = 500 mA, (MIN = 475 mA)
				11b = 1000 mA, (MIN = 900 mA)
				See the LS3 current limit specification in for more details.
1-0	LS2ILIM	R/W	00b	Load switch 2 (LS2) current limit selection:
				00b = 100 mA, (MIN = 94 mA)
				01b = 200 mA, (MIN = 188 mA)
				10b = 500 mA, (MIN = 465 mA)
				11b = 1000 mA, (MIN = 922 mA)
				See the LS2 current limit specification in for more details.



7.5.18 CONFIG3 Register (subaddress = 0x15) [reset = 0x0]

CONFIG3 is shown in Figure 7-44 and described in Table 7-20.

Return to Table 7-5.

Password protected.

Figure 7-44. CONFIG3 Register

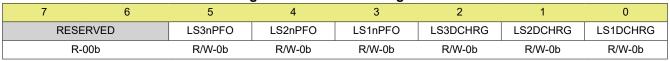


Table 7-20. CONFIG3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	
5	LS3nPFO	R/W	0b	Load switch 3 power-fail disable bit: 0b = Load switch status is not affected by power-fail comparator. 1b = Load switch is disabled if power-fail comparator trips (nPFO is low).
4	LS2nPFO	R/W	0b	Load switch 2 power-fail disable bit: 0b = Load switch status is not affected by power-fail comparator. 1b = Load switch is disabled if power-fail comparator trips (nPFO is low).
3	LS1nPFO	R/W	0b	Load switch 1 power-fail disable bit: 0b = Load switch status is not affected by power-fail comparator. 1b = Load switch is disabled if power-fail comparator trips (nPFO is low).
2	LS3DCHRG	R/W	0b	Load switch 3 discharge enable bit: 0b = Active discharge is disabled. 1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF).
1	LS2DCHRG	R/W	0b	Load switch 2 discharge enable bit: 0b = Active discharge is disabled. 1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF).
0	LS1DCHRG	R/W	0b	Load switch 1 discharge enable bit: 0b = Active discharge is disabled. 1b = Active discharge is enabled (load switch output is actively discharged when switch is OFF).

7.5.19 DCDC1 Register (offset = 0x16) [reset = 0xB5]

DCDC1 is shown in Figure 7-45 and described in Table 7-21.

Return to Table 7-5.

Note 1: This register is password protected. For more information, see Section 7.5.1.

Note 2: A 5-ms blanking time of the over-voltage and under-voltage monitoring occurs when a write is performed on the DCDC1 register.

Note 3: To change the output voltage of DCDC1, the GO bit or the GODSBL bit must be set to 1b in register 0x1A.

Figure 7-45. DCDC1 Register



Table 7-21. DCDC1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	PFM	R/W	1b	Pulse Frequency Modulation (PFM, also known as pulse-skip-mode) enable. PFM mode improves light-load efficiency. Actual PFM mode operation depends on load condition. 0b = Disabled (forced PWM) 1b = Enabled
6	RESERVED	R	0b	



Table 7-21. DCDC1 Register Field Descriptions (continued)

Bit		Туре	Reset	Description (continued)
5-0	DCDC1	R/W	35h	DCDC1 output voltage setting:
				0h = 0.850
				1h = 0.860
				2h = 0.870
				3h = 0.880
				4h = 0.890
				5h = 0.900
				6h = 0.910
				7h = 0.920
				8h = 0.930
				9h = 0.940
				Ah = 0.950
				Bh = 0.960
				Ch = 0.970
				Dh = 0.980
				Eh = 0.990
				Fh = 1.000
				10h = 1.010
				11h = 1.020
				12h = 1.030
				13h = 1.040
				14h = 1.050
				15h = 1.060
				16h = 1.070
				17h = 1.080
				18h = 1.090
				19h = 1.100
				1Ah = 1.110
				1Bh = 1.120
				1Ch = 1.130
				1Dh = 1.140
				1Eh = 1.150
				1Fh = 1.160
				20h = 1.170
				21h = 1.180
				22h = 1.190
				23h = 1.200

Table 7-21. DCDC1 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
		31 , -		24h = 1.210
				25h = 1.220
				26h = 1.230
				27h = 1.240
				28h = 1.250
				29h = 1.260
				2Ah = 1.270
				2Bh = 1.280
				2Ch = 1.290
				2Dh = 1.300
				2Eh = 1.310
				2Fh = 1.320
				30h = 1.330
				31h = 1.340
				32h = 1.350
				33h = 1.375
				34h = 1.400
				35h = 1.425
				36h = 1.450
				37h = 1.475
				38h = 1.500
				39h = 1.525
				3Ah = 1.550
				3Bh = 1.575
				3Ch = 1.600
				3Dh = 1.625
				3Eh = 1.650
				3Fh = 1.675
				JEH - 1.073

7.5.20 DCDC2 Register (subaddress = 0x17) [reset = 0xB5]

DCDC2 is shown in Figure 7-46 and described in Table 7-22.

Return to Table 7-5.

Note 1: This register is password protected. For more information, see Section 7.5.1.

Note 2: A 5-ms blanking time of the over-voltage and under-voltage monitoring occurs when a write is performed on the DCDC2 register.

Note 3: To change the output voltage of DCDC2, the GO bit or the GODSBL bit must be set to 1b in register 0x1A.

Figure 7-46. DCDC2 Register

7	6	5	4	3	2	1	0
PFM	RESERVED	DCDC2					
R/W-1b	R-0b			R/W	/-35h		

Table 7-22. DCDC2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	PFM	R/W	1b	Pulse frequency modulation (PFM, also known as pulse-skip-mode) enable. PFM mode improves light-load efficiency. Actual PFM mode operation depends on load condition. 0b = Disabled (forced PWM) 1b = Enabled



Table 7-22. DCDC2 Register Field Descriptions (continued)

Bit	Field	Type	Reset	Description (Continued)
6	RESERVED	R	0b	
5-0	DCDC2	R/W	35h	DCDC2 output voltage setting:
				0h = 0.850
				1h = 0.860
				2h = 0.870
				3h = 0.880
				4h = 0.890
				5h = 0.900
				6h = 0.910
				7h = 0.920
				8h = 0.930
				9h = 0.940
				Ah = 0.950
				Bh = 0.960
				Ch = 0.970
				Dh = 0.980
				Eh = 0.990
				Fh = 1.000
				10h = 1.010
				11h = 1.020
				12h = 1.030
				13h = 1.040
				14h = 1.050
				15h = 1.060
				16h = 1.070
				17h = 1.080
				18h = 1.090 19h = 1.100
				1Ah = 1.110
				1Bh = 1.120
				1Ch = 1.130
				1Dh = 1.140
				1Eh = 1.150
				1Fh = 1.160
				20h = 1.170
				21h = 1.180
				22h = 1.190
				23h = 1.200
	I		I	· · · · ·

Table 7-22. DCDC2 Register Field Descriptions (continued)

Bit Field Type Reset Description 24h = 1.210 25h = 1.220 26h = 1.230 27h = 1.240 28h = 1.250 29h = 1.260 24h = 1.270 28h = 1.280 29h = 1.280 20h = 1.300 22h = 1.310 27h = 1.310 27h = 1.310 27h = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 34h = 1.500 39h = 1.525 34h = 1.550 38h = 1.575 36h = 1.600 30h = 1.625 32h = 1.650 37h = 1.655 36h = 1.650 37h = 1.675 37h = 1.675			22. DCDC2		rieia Descriptions (continuea)
25h = 1.220 26h = 1.230 27h = 1.240 28h = 1.250 29h = 1.260 2Ah = 1.270 2Bh = 1.280 2Ch = 1.300 2Ch = 1.300 2Fh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650	Bit	Field	Туре	Reset	Description
26h = 1.230 27h = 1.240 28h = 1.250 29h = 1.260 2Ah = 1.270 28h = 1.280 2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.455 36h = 1.455 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					24h = 1.210
27h = 1.240 28h = 1.250 29h = 1.260 22h = 1.270 28h = 1.280 20h = 1.300 22h = 1.300 22h = 1.310 22h = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.455 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 38h = 1.550 38h = 1.575 30h = 1.650					25h = 1.220
28h = 1.250 29h = 1.260 2Ah = 1.270 2Bh = 1.280 2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 38h = 1.555 38h = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					26h = 1.230
29h = 1.260 2Ah = 1.270 2Bh = 1.280 2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					27h = 1.240
2Ah = 1.270 2Bh = 1.280 2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 38h = 1.550 38h = 1.550 38h = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					28h = 1.250
2Bh = 1.280 2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					29h = 1.260
2Ch = 1.290 2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 38h = 1.550 38h = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Ah = 1.270
2Dh = 1.300 2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Bh = 1.280
2Eh = 1.310 2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Ch = 1.290
2Fh = 1.320 30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Dh = 1.300
30h = 1.330 31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Eh = 1.310
31h = 1.340 32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					2Fh = 1.320
32h = 1.350 33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					30h = 1.330
33h = 1.375 34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					31h = 1.340
34h = 1.400 35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					32h = 1.350
35h = 1.425 36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					33h = 1.375
36h = 1.450 37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					34h = 1.400
37h = 1.475 38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					35h = 1.425
38h = 1.500 39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					36h = 1.450
39h = 1.525 3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					
3Ah = 1.550 3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					38h = 1.500
3Bh = 1.575 3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					39h = 1.525
3Ch = 1.600 3Dh = 1.625 3Eh = 1.650					3Ah = 1.550
3Dh = 1.625 3Eh = 1.650					3Bh = 1.575
3Eh = 1.650					3Ch = 1.600
3Fh = 1.675					3Eh = 1.650
					3Fh = 1.675

7.5.21 DCDC3 Register (subaddress = 0x18) [reset = 0x98]

DCDC3 is shown in Figure 7-47 and described in Table 7-23.

Return to Table 7-5.

Note 1: This register is password protected. For more information, see Section 7.5.1.

Note 2: A 5-ms blanking time of the over-voltage and under-voltage monitoring occurs when a write is performed on the DCDC3 register.

Note

Power-up default may differ depending on RSEL value. See Section 7.3.1.13 for details.

Figure 7-47. DCDC3 Register

7	6	5	4	3	2	1	0		
PFM	RESERVED		DCDC3						
R/W-1b	R-0b			R/W	′-18h				

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Table 7-23. DCDC3 Register Field Descriptions

Sit Field Type Reset Description	
5-0 DCDC3 R/W 18h DCDC3 output voltage setting: 0h = 0.900 1h = 0.925 2h = 0.950 3h = 0.975 4h = 1.000 5h = 1.025 6h = 1.050 7h = 1.075 8h = 1.100 9h = 1.125 Ah = 1.150 Bh = 1.175 Ch = 1.200 Dh = 1.225 Eh = 1.250 Fh = 1.250 Fh = 1.350 13h = 1.375 14h = 1.400 15h = 1.425 16h = 1.450 17h = 1.475 18h = 1.500	
0h = 0.900 1h = 0.925 2h = 0.950 3h = 0.975 4h = 1.025 6h = 1.025 6h = 1.050 7h = 1.075 8h = 1.100 9h = 1.125 Ah = 1.150 Bh = 1.175 Ch = 1.200 Dh = 1.225 Eh = 1.250 Fh = 1.275 10h = 1.300 11h = 1.325 12h = 1.350 13h = 1.375 14h = 1.400 15h = 1.425 16h = 1.450 17h = 1.475 18h = 1.500	
1Ah = 1.550 1Bh = 1.600 1Ch = 1.650 1Dh = 1.700 1Eh = 1.750 1Fh = 1.800 20h = 1.850 21h = 1.900 22h = 1.950	

Table 7-23. DCDC3 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
Dit	I ICIU	туре	Reset	
				24h = 2.050
				25h = 2.100
				26h = 2.150
				27h = 2.200
				28h = 2.250
				29h = 2.300
				2Ah = 2.350
				2Bh = 2.400
				2Ch = 2.450
				2Dh = 2.500
				2Eh = 2.550
				2Fh = 2.600
				30h = 2.650
				31h = 2.700
				32h = 2.750
				33h = 2.800
				34h = 2.850
				35h = 2.900
				36h = 2.950
				37h = 3.000
				38h = 3.050
				39h = 3.100
				3Ah = 3.150
				3Bh = 3.200
				3Ch = 3.250
				3Dh = 3.300
				3Eh = 3.350
				3Fh = 3.400
			I.	

7.5.22 DCDC4 Register (subaddress = 0x19) [reset = 0xB2]

DCDC4 is shown in Figure 7-48 and described in Table 7-24.

Return to Table 7-5.

Note 1: This register is password protected. For more information, see Section 7.5.1.

Note 2: A 5-ms blanking time of the over-voltage and under-voltage monitoring occurs when a write is performed on the DCDC4 register.

Note

Power-up default may differ depending on RSEL value. See Section 7.3.1.13 for details. The Reserved setting should not be selected and the output voltage settings should not be modified while the converter is operating.

Figure 7-48. DCDC4 Register

7	6	5	4	3	2	1	0	
PFM	RESERVED	DCDC4						
R/W-1b	R-0b			R/W	-32h			



Table 7-24. DCDC4 Register Field Descriptions

Bit	Field	Type	Reset	Description
7	PFM	R/W	1b	
	I I IVI	I V V V	Ib	Pulse Frequency Modulation (PFM, also known as pulse-skip-mode) enable. PFM mode improves light-load efficiency. Actual PFM mode
				operation depends on load condition.
				0b = Disabled (forced PWM)
				1b = Enabled
6	RESERVED	R	0b	
5-0	DCDC4	R/W	32h	DCDC4 output voltage setting:
3-0	D0D04	I V/ VV	3211	Oh = 1.175
				1h = 1.200
				2h = 1.225
				3h = 1.250
				4h = 1.275
				5h = 1.300
				6h = 1.325
				7h = 1.350
				8h = 1.375
				9h = 1.400
				Ah = 1.425
				Bh = 1.450
				Ch = 1.475
				Dh = 1.500
				Eh = 1.525
				Fh = 1.550
				10h = 1.600
				11h = 1.650
				12h = 1.700
				13h = 1.750
				14h = 1.800
				15h = 1.850
				16h = 1.900
				17h = 1.950
				18h = 2.000
				19h = 2.050
				1Ah = 2.100
				1Bh = 2.150
				1Ch = 2.200
				1Dh = 2.250 1Eh = 2.300
				1Fh = 2.3500
				20h = 2.400
				21h = 2.450
				22h = 2.500
				23h = 2.550
	1			

Table 7-24. DCDC4 Register Field Descriptions (continued)

Bit Field Type Reset Description 24h = 2 25h = 2 25h = 2 26h = 2 27h = 2	.600 .650 .700
25h = 2 26h = 2 27h = 2	.700 .750
26h = 2 27h = 2	.700 .750
27h = 2	.750
28h = 2	
29h = 2	
2Ah = 2	
2Bh = 2	
2Ch = 3	
2Dh = 3	
2Eh = 3	
2Fh = 3	
30h = 3	
31h = 3	.250
32h = 3	.300
33h = 3	.350
34h = 3	.400
35h = re	eserved
36h = re	eserved
37h = re	eserved
38h = re	eserved
39h = re	eserved
3Ah = re	eserved
3Bh = re	eserved
3Ch = r	eserved
3Dh = r	eserved
3Eh = re	eserved
3Fh = re	eserved

7.5.23 SLEW Register (subaddress = 0x1A) [reset = 0x06]

SLEW is shown in Figure 7-49 and described in Table 7-25.

Return to Table 7-5.

Note

Slew-rate control applies to DCDC1 and DCDC2 only. If changing from a higher voltage to lower voltage while STRICT = 1 and converters are in a no load state, PFM bit for DCDC1 and DCDC2 must be set to 0.

Figure 7-49. SLEW Register

7	6	5	4	3	2	1	0
GO	GODSBL		RESERVED			SLEW	
R/W-0b	R/W-0b		R-000b			R/W-6h	

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Table 7-25. SLEW Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	GO	R/W	0b	Go bit. Note: Bit is automatically reset at the end of the voltage transition. 0b = No change 1b = Initiates the transition from present state to the output voltage setting currently stored in DCDC1 and DCDC2 register. SLEW setting does apply.
6	GODSBL	R/W	Ob	Go disable bit 0b = Enabled 1b = Disabled; DCDC1 and DCDC2 output voltage changes whenever set-point is updated in DCDC1 and DCDC2 register without having to write to the GO bit. SLEW setting does apply.
5-3	RESERVED	R	000b	
2-0	SLEW	R/W	6h	Output slew rate setting: 0h = 160 µs/step (0.0625 mV/µs at 10 mV per step) 1h = 80 µs/step (0.125 mV/µs at 10 mV per step) 2h = 40 µs/step (0.250 mV/µs at 10 mV per step) 3h = 20 µs/step (0.500 mV/µs at 10 mV per step) 4h = 10 µs/step (1.0 mV/µs at 10 mV per step) 5h = 5 µs/step (2.0 mV/µs at 10 mV per step) 6h = 2.5 µs/step (4.0 mV/µs at 10 mV per step) 7h = Immediate; slew rate is only limited by control loop response time. Note: The actual slew rate depends on the voltage step per code. Refer to DCDCx registers for details.

7.5.24 LDO1 Register (subaddress = 0x1B) [reset = 0x1F]

LDO1 is shown in Figure 7-50 and described in Table 7-26.

Return to Table 7-5.

Note 1: This register is password protected. For more information, see Section 7.5.1.

Note 2: A 5-ms blanking time of the over-voltage and under-voltage monitoring occurs when a write is performed on the LDO1 register.

Figure 7-50. LDO1 Register



Table 7-26. LDO1 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	00b	

Table 7-26, LDO1 Register Field Descriptions (continued)

	Table 7-26. LDO1 Register Field Descriptions (continued)						
Bit	Field	Туре	Reset	Description			
5-0	LDO1	R/W	1Fh	LDO1 output voltage setting:			
				0h = 0.900			
				1h = 0.925			
				2h = 0.950			
				3h = 0.975			
				4h = 1.000			
				5h = 1.025			
				6h = 1.050			
				7h = 1.075			
				8h = 1.100			
				9h = 1.125			
				Ah = 1.150			
				Bh = 1.175			
				Ch = 1.200			
				Dh = 1.225			
				Eh = 1.250			
				Fh = 1.275			
				10h = 1.300			
				11h = 1.325			
				12h = 1.350			
				13h = 1.375			
				14h = 1.400			
				15h = 1.425			
				16h = 1.450			
				17h = 1.475			
				18h = 1.500			
				19h = 1.525			
1	T. Control of the Con	T. Control of the Con	1	ı L			



Table 7-26. LDO1 Register Field Descriptions (continued)

				eld Descriptions (continued)
Bit	Field	Туре	Reset	Description
				1Ah = 1.550
				1Bh = 1.600
				1Ch = 1.650
				1Dh = 1.700
				1Eh = 1.750
				1Fh = 1.800
				20h = 1.850
				21h = 1.900
				22h = 1.950
				23h = 2.000
				24h = 2.050
				25h = 2.100
				26h = 2.150
				27h = 2.200
				28h = 2.250
				29h = 2.300
				2Ah = 2.350
				2Bh = 2.400
				2Ch = 2.450
				2Dh = 2.500
				2Eh = 2.550
				2Fh = 2.600
				30h = 2.650
				31h = 2.700
				32h = 2.750
				33h = 2.800
				34h = 2.850
				35h = 2.900
				36h = 2.950
				37h = 3.000
				38h = 3.050
				39h = 3.100
				3Ah = 3.150
				3Bh = 3.200
				3Ch = 3.250
				3Dh = 3.300
				3Eh = 3.350
				3Fh = 3.400
			l	

7.5.25 SEQ1 Register (subaddress = 0x20) [reset = 0x00]

SEQ1 is shown in Figure 7-51 and described in Table 7-27.

Return to Table 7-5.

Password protected.

Figure 7-51. SEQ1 Register

7	6	5	4	3	2	1	0
DLY8	DLY7	DLY6	DLY5	DLY4	DLY3	DLY2	DLY1
R/W-0b							

Table 7-27. SEQ1 Register Field Descriptions

Table 7-27. SEQ1 Register Field Descriptions						
Bit	Field	Туре	Reset	Description		
7	DLY8	R/W	Ob	Delay8 (occurs after Strobe 8 and before Strobe 9.) 0b = 2 ms 1b = 5 ms		
6	DLY7	R/W	0b	Delay7 (occurs after Strobe 7 and before Strobe 8.) 0b = 2 ms 1b = 5 ms		
5	DLY6	R/W	Ob	Delay6 (occurs after Strobe 6 and before Strobe 7.) 0b = 2 ms 1b = 5 ms		
4	DLY5	R/W	Ob	Delay5 (occurs after Strobe 5 and before Strobe 6.) 0b = 2 ms 1b = 5 ms		
3	DLY4	R/W	Ob	Delay4 (occurs after Strobe 4 and before Strobe 5.) 0b = 2 ms 1b = 5 ms		
2	DLY3	R/W	Ob	Delay3 (occurs after Strobe 3 and before Strobe 4.) 0b = 2 ms 1b = 5 ms		
1	DLY2	R/W	Ob	Delay2 (occurs after Strobe 2 and before Strobe 3.) 0b = 2 ms 1b = 5 ms		
0	DLY1	R/W	Ob	Delay1 (occurs after Strobe 1 and before Strobe 2.) 0b = 2 ms 1b = 5 ms		

7.5.26 SEQ2 Register (subaddress = 0x21) [reset = 0x00]

SEQ2 is shown in Figure 7-52 and described in Table 7-28.

Return to Table 7-5.

Password protected.

Figure 7-52. SEQ2 Register

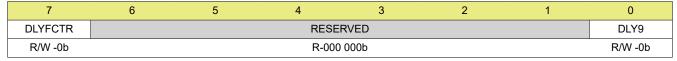


Table 7-28. SEQ2 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7	DLYFCTR	R/W	0b	Power-down delay factor:
				0b = 1x
				1b = 10x (delay times are multiplied by 10x during power-down.)
				Note: DLYFCTR has no effect on power-up timing.
6-1	RESERVED	R	000 000b	
0	DLY9	R/W	0b	Delay9 (occurs after Strobe 9 and before Strobe 10.)
				0b = 2 ms
				1b = 5 ms

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7.5.27 SEQ3 Register (subaddress = 0x22)[reset = 0x55]

SEQ3 is shown in Figure 7-53 and described in Table 7-29.

Return to Table 7-5.

Password protected.

Figure 7-53. SEQ3 Register

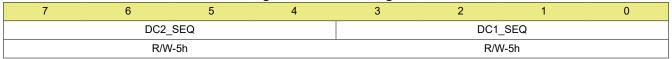


Table 7-29. SEQ3 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	DC2_SEQ	R/W	5h	DCDC2 enable STROBE:
				0h = Rail is not controlled by sequencer.
				1h = Rail is not controlled by sequencer.
				2h = Rail is not controlled by sequencer.
				3h = Enable at STROBE 3.
				4h = Enable at STROBE 4.
				5h = Enable at STROBE 5.
				6h = Enable at STROBE 6.
				7h = Enable at STROBE 7.
				8h = Enable at STROBE 8.
				9h = Enable at STROBE 9.
				Ah = Enable at STROBE 10.
				Bh = Rail is not controlled by sequencer.
				Ch = Rail is not controlled by sequencer.
				Dh = Rail is not controlled by sequencer.
				Eh = Rail is not controlled by sequencer.
				Fh = Rail is not controlled by sequencer.
3-0	DC1_SEQ	R/W	5h	DCDC1 enable STROBE:
				0h = Rail is not controlled by sequencer.
				1h = Rail is not controlled by sequencer.
				2h = Rail is not controlled by sequencer.
				3h = Enable at STROBE 3.
				4h = Enable at STROBE 4.
				5h = Enable at STROBE 5.
				6h = Enable at STROBE 6.
				7h = Enable at STROBE 7.
				8h = Enable at STROBE 8.
				9h = Enable at STROBE 9.
				Ah = Enable at STROBE 10.
				Bh = Rail is not controlled by sequencer.
				Ch = Rail is not controlled by sequencer.
				Dh = Rail is not controlled by sequencer.
				Eh = Rail is not controlled by sequencer.
				Fh = Rail is not controlled by sequencer.

7.5.28 SEQ4 Register (subaddress = 0x23) [reset = 0x37]

SEQ4 is shown in Figure 7-54 and described in Table 7-30.

Return to Table 7-5.

Password protected.

Figure 7-54. SEQ4 Register

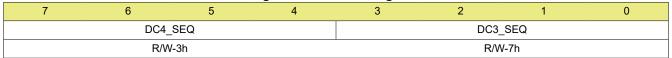


Table 7-30. SEQ4 Register Field Descriptions

	Table 7-30. SEQ4 Register Field Descriptions							
Bit	Field	Туре	Reset	Description				
7-4	DC4_SEQ	R/W	3h	DCDC4 enable STROBE:				
				0h = Rail is not controlled by sequencer.				
				1h = Rail is not controlled by sequencer.				
				2h = Rail is not controlled by sequencer.				
				3h = Enable at STROBE 3.				
				4h = Enable at STROBE 4.				
				5h = Enable at STROBE 5.				
				6h = Enable at STROBE 6.				
				7h = Enable at STROBE 7.				
				8h = Enable at STROBE 8.				
				9h = Enable at STROBE 9.				
				Ah = Enable at STROBE 10.				
				Bh = Rail is not controlled by sequencer.				
				Ch = Rail is not controlled by sequencer.				
				Dh = Rail is not controlled by sequencer.				
				Eh = Rail is not controlled by sequencer.				
				Fh = Rail is not controlled by sequencer.				
3-0	DC3_SEQ	R/W	7h	DCDC3 enable STROBE:				
				0h = Rail is not controlled by sequencer.				
				1h = Rail is not controlled by sequencer.				
				2h = Rail is not controlled by sequencer.				
				3h = Enable at STROBE 3.				
				4h = Enable at STROBE 4.				
				5h = Enable at STROBE 5.				
				6h = Enable at STROBE 6.				
				7h = Enable at STROBE 7.				
				8h = Enable at STROBE 8.				
				9h = Enable at STROBE 9.				
				Ah = Enable at STROBE 10.				
				Bh = Rail is not controlled by sequencer.				
				Ch = Rail is not controlled by sequencer.				
				Dh = Rail is not controlled by sequencer.				
				Eh = Rail is not controlled by sequencer.				
				Fh = Rail is not controlled by sequencer.				

7.5.29 SEQ5 Register (subaddress = 0x24) [reset = 0x00]

SEQ5 is shown in Figure 7-55 and described in Table 7-31.

Return to Table 7-5.

Password protected.

Figure 7-55. SEQ5 Register

7	6	5	4	3	2	1	0
RESERVED		DC6	_SEQ	RESE	RVED	DC5_	_SEQ

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Figure 7-55. SEQ5 Register (continued)

R-0h R/W-0h R-0h R/W-0h

Table 7-31. SEQ5 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-6	RESERVED	R	0h	
5-4	DC6_SEQ	R/W	Oh	DCDC6 enable STROBE. Note: STROBE 1 and STROBE 2 are executed only if FSEAL = 0. DCDC5 and 6 cannot be disabled by sequencer once freshness seal is broken. 0h = Rail is not controlled by sequencer. 1h = Enable at STROBE 1. 2h = Enable at STROBE 2. 3h = Rail is not controlled by sequencer.
3-2	RESERVED	R	0h	
1-0	DC5_SEQ	R/W	Oh	DCDC5 enable STROBE. Note: STROBE 1 and STROBE 2 are executed only if FSEAL = 0. DCDC5 and 6 cannot be disabled by sequencer once freshness seal is broken. 0h = Rail is not controlled by sequencer. 1h = Enable at STROBE 1. 2h = Enable at STROBE 2. 3h = Rail is not controlled by sequencer.

7.5.30 SEQ6 Register (subaddress = 0x25) [reset = 0xA8]

SEQ6 is shown in Figure 7-56 and described in Table 7-32.

Return to Table 7-5.

Password protected.

Figure 7-56. SEQ6 Register

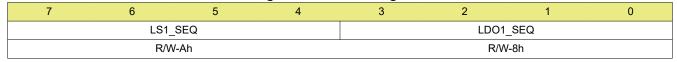


Table 7-32. SEQ6 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	LS1_SEQ	R/W	Ah	LS1 enable STROBE:
				0h = Rail is not controlled by sequencer.
				1h = Rail is not controlled by sequencer.
				2h = Rail is not controlled by sequencer.
				3h = Enable at STROBE 3.
				4h = Enable at STROBE 4.
				5h = Enable at STROBE 5.
				6h = Enable at STROBE 6.
				7h = Enable at STROBE 7.
				8h = Enable at STROBE 8.
				9h = Enable at STROBE 9.
				Ah = Enable at STROBE 10.
				Bh = Rail is not controlled by sequencer.
				Ch = Rail is not controlled by sequencer.
				Dh = Rail is not controlled by sequencer.
				Eh = Rail is not controlled by sequencer.
				Fh = Rail is not controlled by sequencer.

Table 7-32. SEQ6 Register Field Descriptions (continued)

	Table 7-32. SEQ6 Register Field Descriptions (Continued)						
Bit	Field	Туре	Reset	Description			
3-0	LDO1_SEQ	R/W	8h	LDO1 enable STROBE:			
				0h = Rail is not controlled by sequencer.			
				1h = Rail is not controlled by sequencer.			
				2h = Rail is not controlled by sequencer.			
				3h = Enable at STROBE 3.			
				4h = Enable at STROBE 4.			
				5h = Enable at STROBE 5.			
				6h = Enable at STROBE 6.			
				7h = Enable at STROBE 7.			
				8h = Enable at STROBE 8.			
				9h = Enable at STROBE 9.			
				Ah = Enable at STROBE 10.			
				Bh = Rail is not controlled by sequencer.			
				Ch = Rail is not controlled by sequencer.			
				Dh = Rail is not controlled by sequencer.			
				Eh = Rail is not controlled by sequencer.			
				Fh = Rail is not controlled by sequencer.			

7.5.31 SEQ7 Register (subaddress = 0x26) [reset = 0x09]

SEQ7 is shown in Figure 7-57 and described in Table 7-33.

Return to Table 7-5.

Password protected.

Figure 7-57. SEQ7 Register

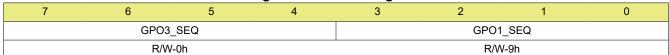


Table 7-33. SEQ7 Register Field Descriptions

Bit	Field	Туре	Reset	Description
7-4	GPO3_SEQ	R/W	0h	GPO3 enable STROBE:
				0h = Rail is not controlled by sequencer.
				1h = Rail is not controlled by sequencer.
				2h = Rail is not controlled by sequencer.
				3h = Enable at STROBE 3.
				4h = Enable at STROBE 4.
				5h = Enable at STROBE 5.
				6h = Enable at STROBE 6.
				7h = Enable at STROBE 7.
				8h = Enable at STROBE 8.
				9h = Enable at STROBE 9.
				Ah = Enable at STROBE 10.
				Bh = Rail is not controlled by sequencer.
				Ch = Rail is not controlled by sequencer.
				Dh = Rail is not controlled by sequencer.
				Eh = Rail is not controlled by sequencer.
				Fh = Rail is not controlled by sequencer.

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Table 7-33. SEQ7 Register Field Descriptions (continued)

Bit	Field	Туре	Reset	Description
3-0	GPO1_SEQ	R/W	9h	GPO1 enable STROBE:
				0h = Rail is not controlled by sequencer.
				1h = Rail is not controlled by sequencer.
				2h = Rail is not controlled by sequencer.
				3h = Enable at STROBE 3.
				4h = Enable at STROBE 4.
				5h = Enable at STROBE 5.
				6h = Enable at STROBE 6.
				7h = Enable at STROBE 7.
				8h = Enable at STROBE 8.
				9h = Enable at STROBE 9.
				Ah = Enable at STROBE 10.
				Bh = Rail is not controlled by sequencer.
				Ch = Rail is not controlled by sequencer.
				Dh = Rail is not controlled by sequencer.
				Eh = Rail is not controlled by sequencer.
				Fh = Rail is not controlled by sequencer.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The TPS6521845 is designed to pair with NXP i.MX 6Solo and 6DualLite processors. The typical application in Section 8.2 is based on and uses terminology consistent with the Sitara™ family of processors.

8.1.1 Applications Without Battery Backup Supplies

In applications that do not require always-on supplies, both inputs and the output of the power-path can simply be grounded. All pins related to DCDC5 and DCDC6 are also tied to ground, and PGOOD_BU and IN_nCC are kept floating. With the backup supplies completely disabled, the FSEAL bit in the STATUS register is undefined and should be ignored.

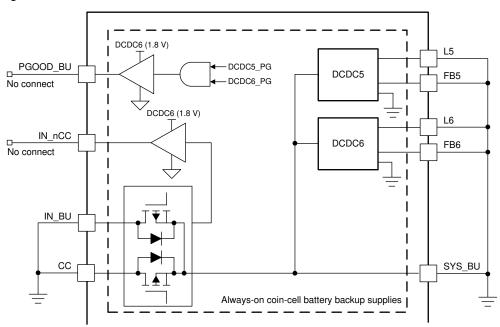


Figure 8-1. DCDC5 and DCDC6 Pins

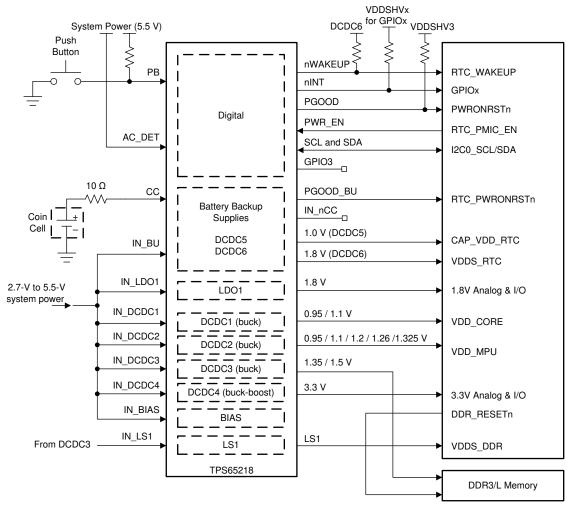
Note

In applications that do not require always-on supplies, PGOOD_BU and IN_nCC can be kept floating. All other pins are tied to ground.

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8.2 Typical Application



A. Block diagram shows TPS65218D0 powering AM437x processor. For TPS6521845, refer to this Tech Note. For TPS6521815, the wiring is not pre-defined and is programmed for the specific processor in the application.

Figure 8-2. Typical Application Schematic for TPS65218D0

8.2.1 Design Requirements

Table 8-1 lists the design requirements.

Table 8-1. Design Parameters for TPS65218D0 (1)

100.00	,	
	VOLTAGE	SEQUENCE
DCDC1	1.1 V	8
DCDC2	1.1 V	9
DCDC3	1.2 V	5
DCDC4	3.3 V	7
DCDC5	1.0 V	2
DCDC6	1.8 V	1
LDO1	1.8 V	3

Default output voltages shown for TPS65218D0. For other TPS65218xx variants, refer to DCDC1-4 and LDO1 registers in Section 7.5.4.

8.2.2 Detailed Design Procedure

8.2.2.1 Output Filter Design

The step down converters (DCDC1, DCDC2, and DCDC3) on TPS6521845 are designed to operate with effective inductance values in the range of 1 to 2.2 μ H and with effective output capacitance in the range of 10 to 100 μ F. The internal compensation is optimized to operate with an output filter of L = 1.5 μ H and C_{OUT} = 10 μ F.

The buck boost converter (DCDC4) on TPS6521845 is designed to operate with effective inductance values in the range of 1.2 to 2.2 μ H. The internal compensation is optimized to operate with an output filter of L = 1.5 μ H and C_{OUT} = 47 μ F.

The two battery backup converters (DCDC5 and DCDC6) are designed to operate with effective inductance values in the range of 4.7 to 22 μ H. The internal compensation is optimized with an output filter of L = 10 μ H and C_{OUT} = 20 μ F.

Larger or smaller inductor/capacitance values can be used to optimize performance of the device for specific operation conditions.

8.2.2.2 Inductor Selection for Buck Converters

The inductor value affects its peak to peak ripple current, the PWM to PFM transition point, the output voltage ripple, and the efficiency. The selected inductor must be rated for its DC resistance and saturation current. The inductor ripple current (ΔL) decreases with higher inductance and increases with higher V_{IN} or V_{OUT} . Equation 1 calculates the maximum inductor current ripple under static load conditions. The saturation current of the inductor should be rated higher than the maximum inductor current as calculated with Equation 2. This is recommended as during heavy load transient the inductor current will rise above the calculated value.

$$\Delta I_{L} = V_{OUT} \times \frac{1 - \frac{V_{OUT}}{V_{IN}}}{L \times f}$$
(1)

$$I_{Lmax} = I_{OUTmax} + \frac{\Delta I_{L}}{2}$$
 (2)

where

- F = Switching frequency
- L = Inductor value
- ΔI_L = Peak-to-peak inductor ripple current
- I_{Lmax} = Maximum inductor current

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The following inductors have been used with the TPS6521845 (see Table 8-2).

Table 8-2. List of Recommended Inductors

PART NUMBER	VALUE	MANUFACTURER						
INDUCTORS FOR DCDC1, DCDC2, DCDC3, DCDC4								
SPM3012T-1R5M	1.5 μH, 2.8 A, 77 mΩ	3.2 × 3.0 × 1.2	TDK					
IHLP1212BZER1R5M11	1.5 μH, 4.0 A, 28.5 mΩ	3.6 × 3.0 × 2.0	Vishay					
INDUCTORS FOR DCDC5, DCDC6	INDUCTORS FOR DCDC5, DCDC6							
MLZ2012N100L	10 μH, 110 mA, 300 mΩ	2012 / 0805 (2.00 × 1.25 × 1.25)	TDK					
LQM21FN100M80	10 μH, 100 mA, 300 mΩ	2012 / 0805 (2.00 × 1.25 × 1.25)	Murata					

8.2.2.3 Output Capacitor Selection

The hysteretic PWM control scheme of the TPS6521845 switching converters allows the use of tiny ceramic capacitors. Ceramic capacitors with low ESR values have the lowest output voltage ripple and are recommended. The output capacitor requires either an X7R or X5R dielectric.

At light load currents the converter operates in power save mode, and the output voltage ripple is dependent on the output capacitor value and the PFM peak inductor current. Higher output capacitor values minimize the voltage ripple in PFM Mode and tighten DC output accuracy in PFM mode.

The two battery backup converters (DCDC5 and DCDC6) always operate in PFM mode. For these converters, a capacitor of at least 20 µF is recommended on the output to help minimize voltage ripple.

The buck-boost converter requires additional output capacitance to help maintain converter stability during high load conditions. At least 40 μ F of output capacitance is recommended and an additional 100-nF capacitor can be added to further filter output ripple at higher frequencies.

Table 8-2 lists the recommended capacitors.

Table 8-3. List of Recommended Capacitors

Table 0 0: Elst of Recommended Supacitors								
PART NUMBER	VALUE	SIZE (mm) [L × W × H]	MANUFACTURER					
CAPACITORS FOR VOLTAGES UP TO 5.5 V ⁽¹⁾								
GRM188R60J105K	1 μF	1608 / 0603 (1.6 × 0.8 × 0.8)	Murata					
GRM21BR60J475K	4.7 μF	2012 / 0805 (2.0 × 1.25 × 1.25)	Murata					
GRM31MR60J106K	10 μF	3216 / 1206 (3.2 × 1.6 × 1.6)	Murata					
GRM31CR60J226K	22 μF	3216 / 1206 (3.2 × 1.6 × 1.6)	Murata					
CAPACITORS FOR VOLTAGES UP TO 3.3 V ⁽¹⁾								
GRM21BR60J106K	10 μF	2012 / 0805 (2.0 × 1.25 × 1.25)	Murata					

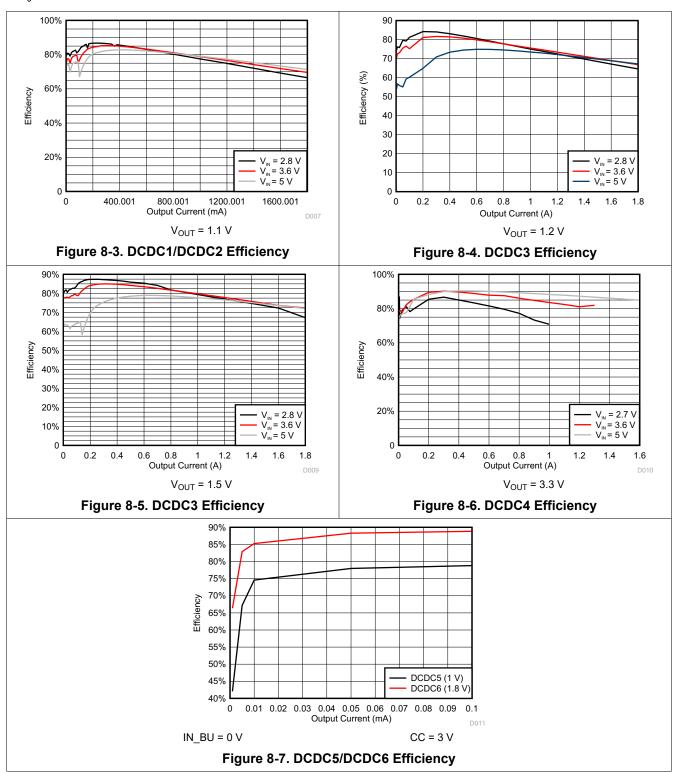
Product Folder Links: TPS6521845

(1) The DC bias effect of ceramic capacitors must be considered when selecting a capacitor.

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8.2.3 Application Curves

at T_J = 25°C unless otherwise noted



9 Power Supply Recommendations

The device is designed to operate with an input voltage supply range between 2.7 V and 5.5 V. This input supply can be from a single cell Li-lon battery or other externally regulated supply. If the input supply is located more than a few inches from the additional bulk capacitance may be required in addition to the ceramic bypass capacitors. An electrolytic capacitor with a value of $47 \, \mu F$ is a typical choice.

The coin cell back up input is designed to operate with a input voltage supply between 2.2 V and 3.3 V This input should be supplied by a coin cell battery with 3-V nominal voltage.

10 Layout

10.1 Layout Guidelines

Follow these layout guidelines:

- The IN_X pins should be bypassed to ground with a low ESR ceramic bypass capacitor. The typical recommended bypass capacitance is 4.7-µF with a X5R or X7R dielectric.
- The optimum placement is closest to the IN_X pins of the device. Take care to minimize the loop area formed by the bypass capacitor connection, the IN X pin, and the thermal pad of the device.
- The thermal pad should be tied to the PCB ground plane with a minimum of 25 vias. See Figure 10-2 for an example.
- The LX trace should be kept on the PCB top layer and free of any vias.
- The FBX traces should be routed away from any potential noise source to avoid coupling.
- DCDC4 Output capacitance should be placed immediately at the DCDC4 pin. Excessive distance between the capacitance and DCDC4 pin may cause poor converter performance.

10.2 Layout Example

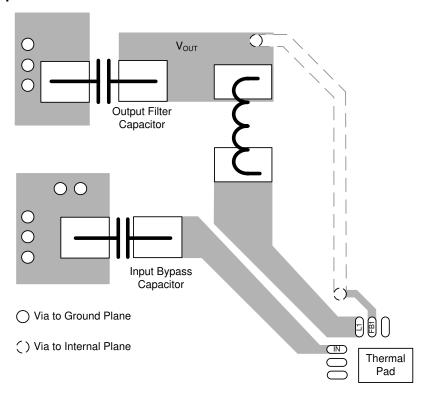
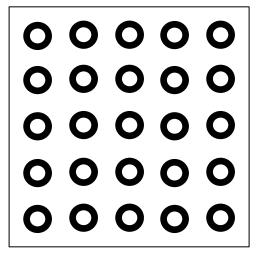


Figure 10-1. Layout Recommendation





Recommended Thermal Pad by size Hole size (s) = 8 mil Diameter (d) = 16 mil



Figure 10-2. PowerPAD™ Layout Recommendation



11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, Basic Calculation of a Buck Converter's Power Stage application report
- Texas Instruments, Design Calculations for Buck-Boost Converters application report
- Texas Instruments, Empowering Designs With Power Management IC (PMIC) for Processor Applications application report
- Texas Instruments, TPS65218EVM user's guide
- Texas Instruments, TPS65218 Power Management Integrated Circuit (PMIC) for Industrial Applications application report

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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11.4 Trademarks

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11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Product Folder Links: TPS6521845

www.ti.com 31-Oct-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
	(1)	(2)			(0)	(4)	(5)		(0)
TPS6521845RSLR	Active	Production	VQFN (RSL) 48	2500 LARGE T&R	Yes	FULL NIPDAU	Level-3-260C-168 HR	-40 to 105	T6521845
TPS6521845RSLR.A	Active	Production	VQFN (RSL) 48	2500 LARGE T&R	Yes	FULL NIPDAU	Level-3-260C-168 HR	-40 to 105	T6521845
TPS6521845RSLT	Active	Production	VQFN (RSL) 48	250 SMALL T&R	Yes	FULL NIPDAU	Level-3-260C-168 HR	-40 to 105	T6521845
TPS6521845RSLT.A	Active	Production	VQFN (RSL) 48	250 SMALL T&R	Yes	FULL NIPDAU	Level-3-260C-168 HR	-40 to 105	T6521845

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

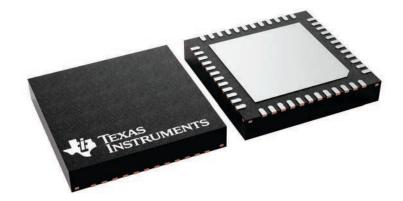
⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

6 x 6, 0.4 mm pitch

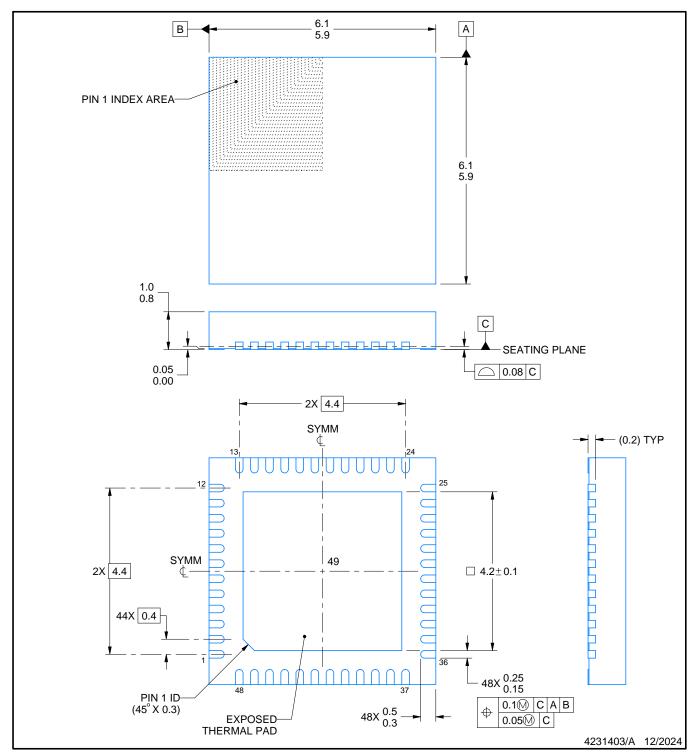
QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





PLASTIC QUAD FLATPACK - NO LEAD

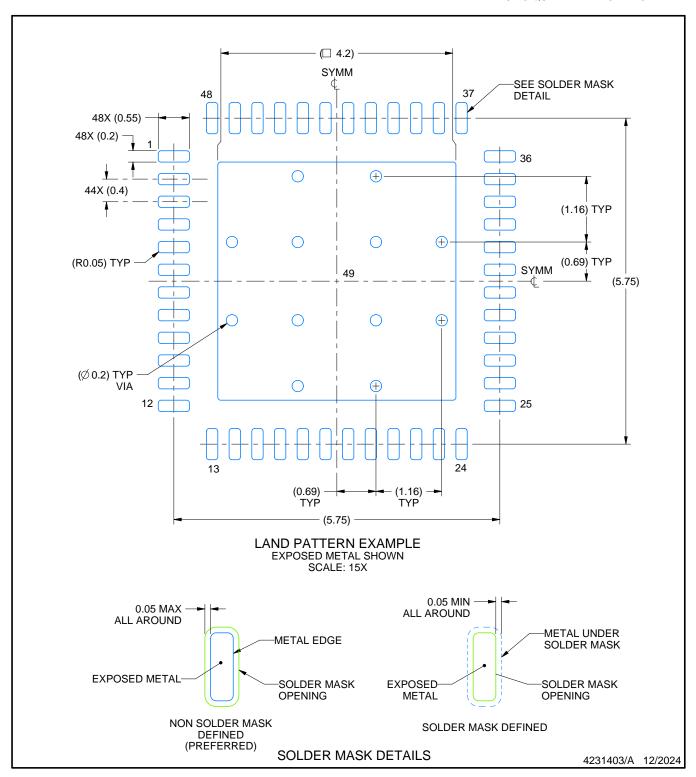


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



PLASTIC QUAD FLATPACK - NO LEAD

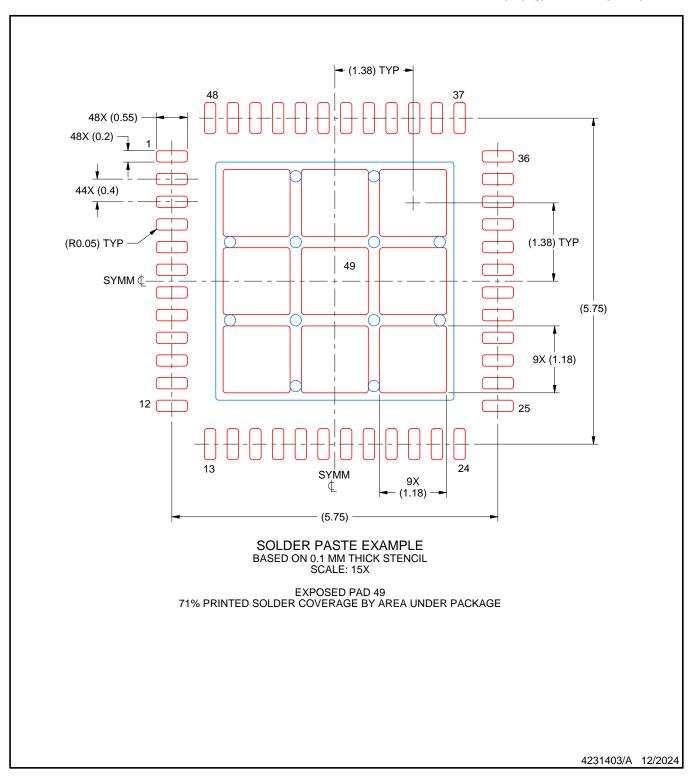


NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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